

LOM3258 Introdução à Eletrônica e Computação Física

Básico de Eletrônica

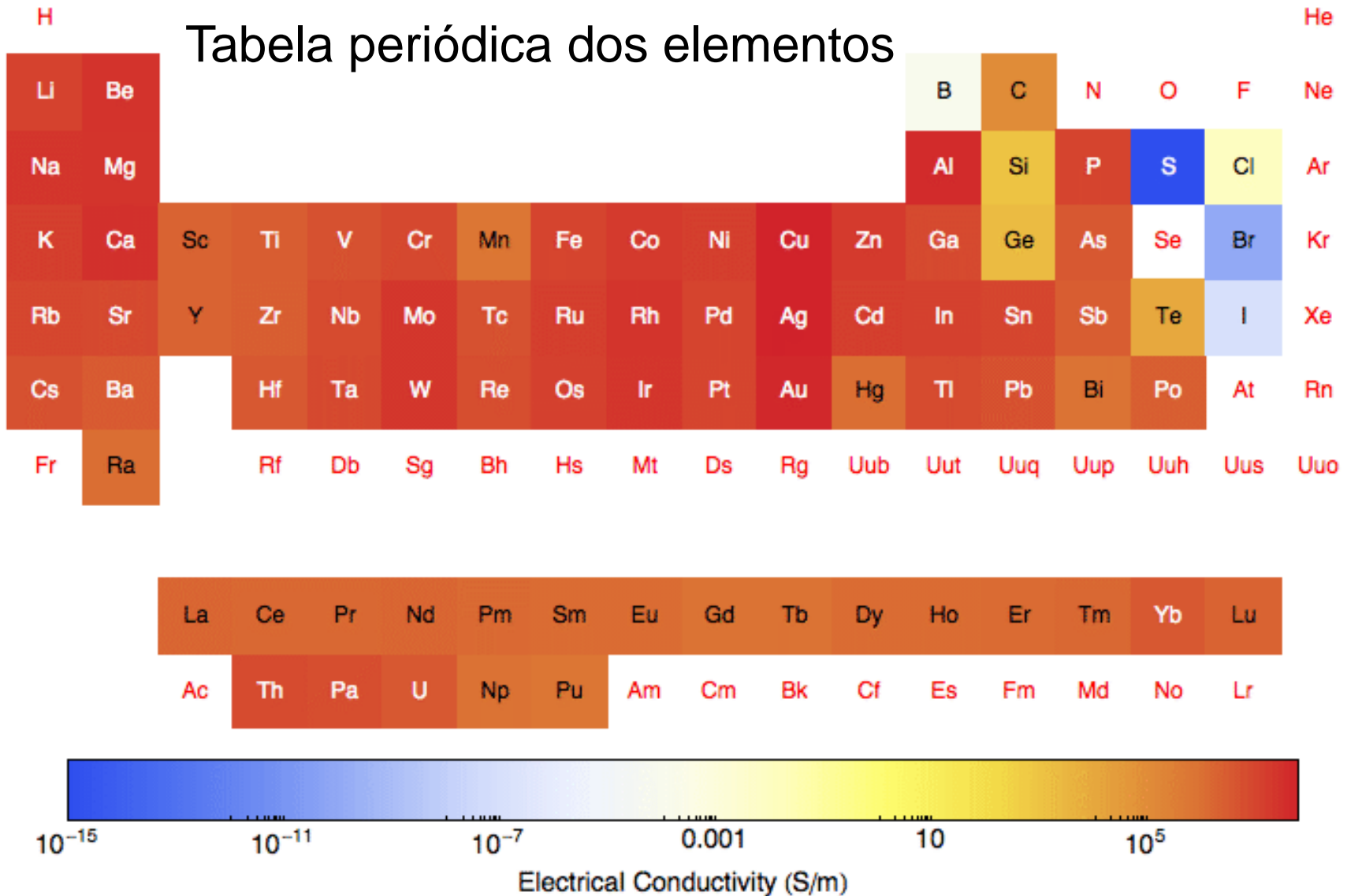
Resistor

Diodo

Transistor

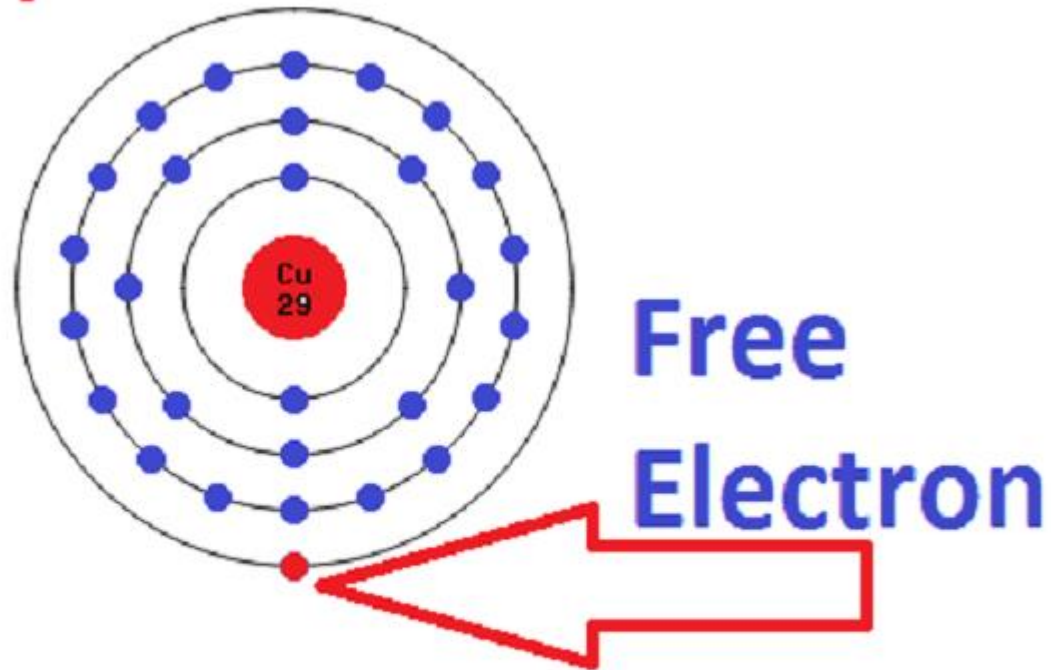
Resistência e condutividade elétrica

Condutividade elétrica dos elementos



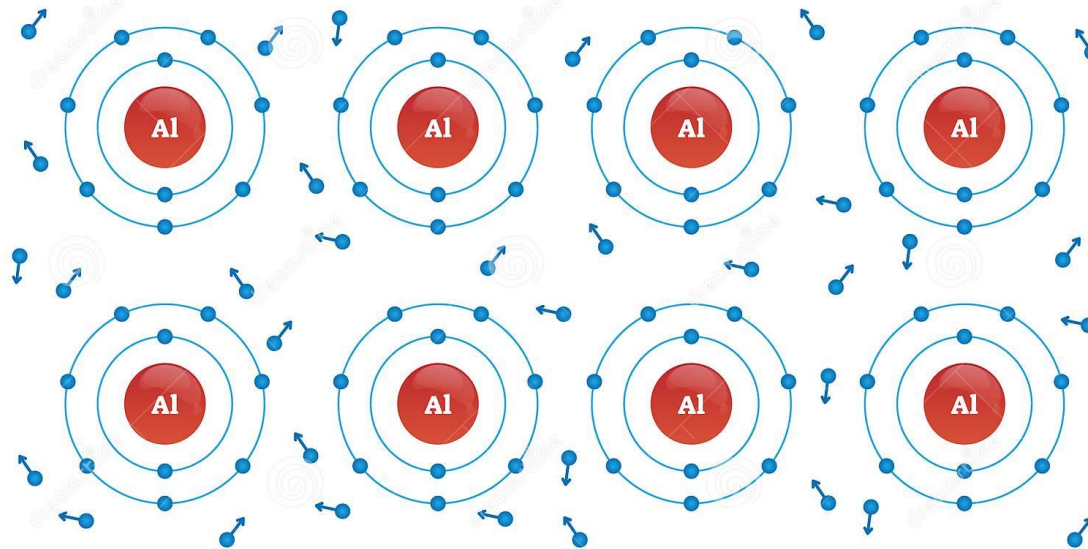
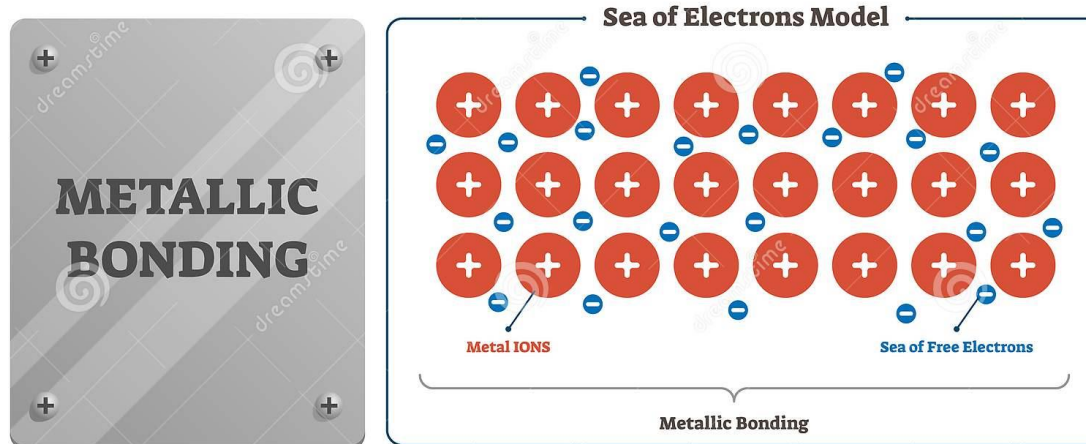
Estrutura eletrônica e condutividade elétrica

Copper Orbit structure



$$k=2, l=8, m=18, \text{ Last } =1$$

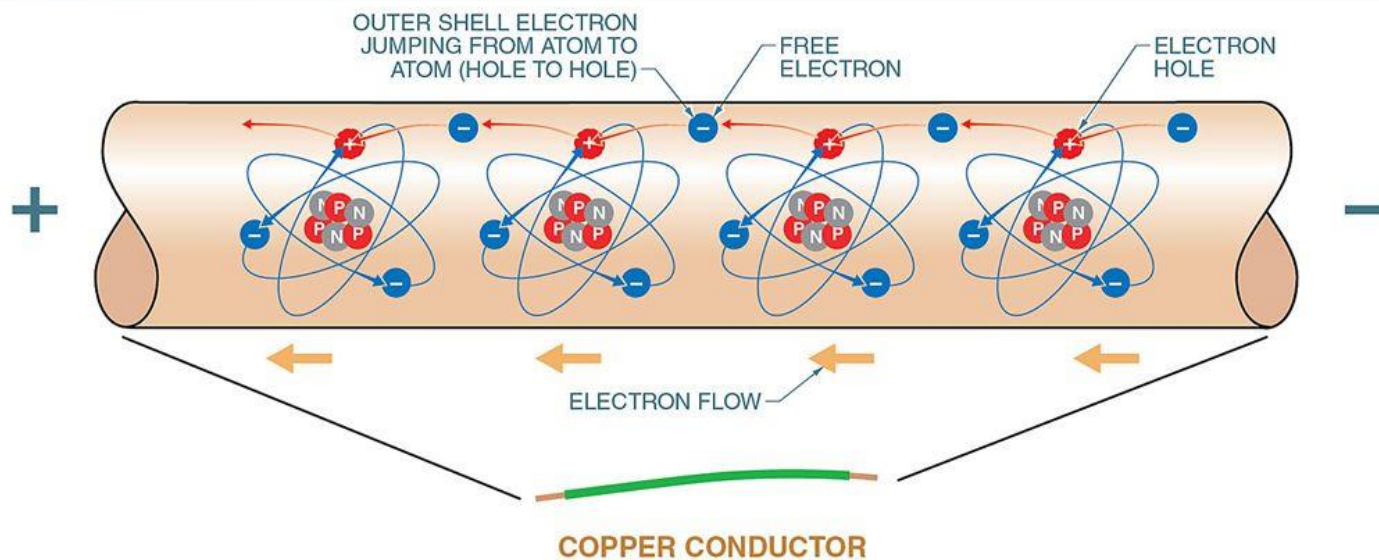
Estrutura eletrônica e condutividade elétrica



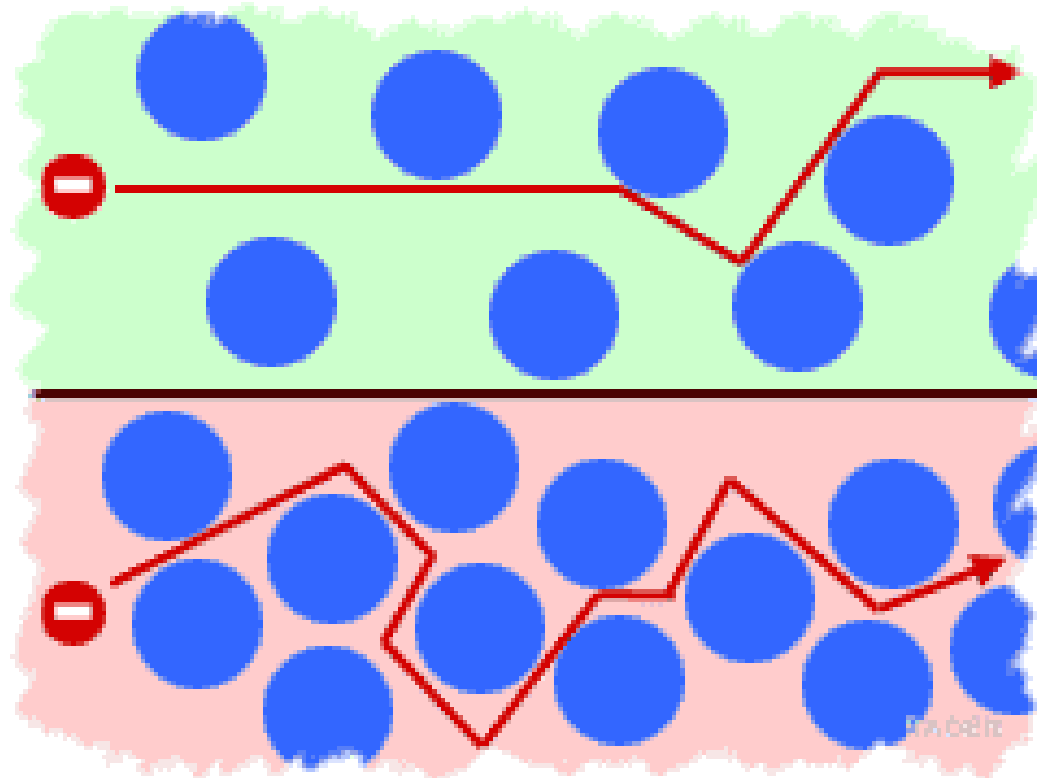
Estrutura eletrônica e condutividade elétrica

A conductor allows free electrons to pass readily through it.

CONDUCTORS



Estrutura eletrônica e condutividade elétrica

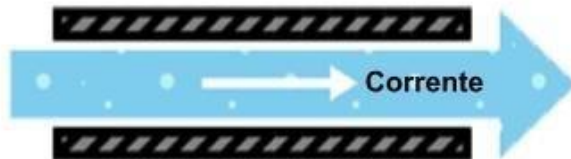


THE SMOOTHER TOP PATH
SHOWS A GOOD CONDUCTOR.
THE BOTTOM IS POOR.

Resistor

Resistor **limita** a corrente

Cano de água
sem resistência permite
corrente máxima.



Cano de água
com resistência que
limita a corrente!

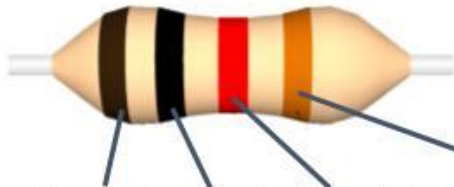


Resistência



Resistor

Exemplo de valor de resistor



4 faixas de cores

Cor	1ª Faixa	2ª Faixa	Nº de zeros/multiplicador	Tolerância
Preto	0	0	x1	
Marrom	1	1	x10	± 1%
Vermelho	2	2	x100	± 2%
Laranja	3	3	x1.000	
Amarelo	4	4	x10.000	
Verde	5	5	x100.000	± 0,5%
Azul	6	6	x1.000.000	± 0,25%
Violeta	7	7	x10.000.000	± 0,1%
Cinza	8	8	x100.000.000	± 0,05%
Branco	9	9	x1.000.000.000	
Dourado			x0,1	± 5%
Prata			x0,01	± 10%

1ª faixa: MARROM = 1

2ª faixa: PRETO = 0

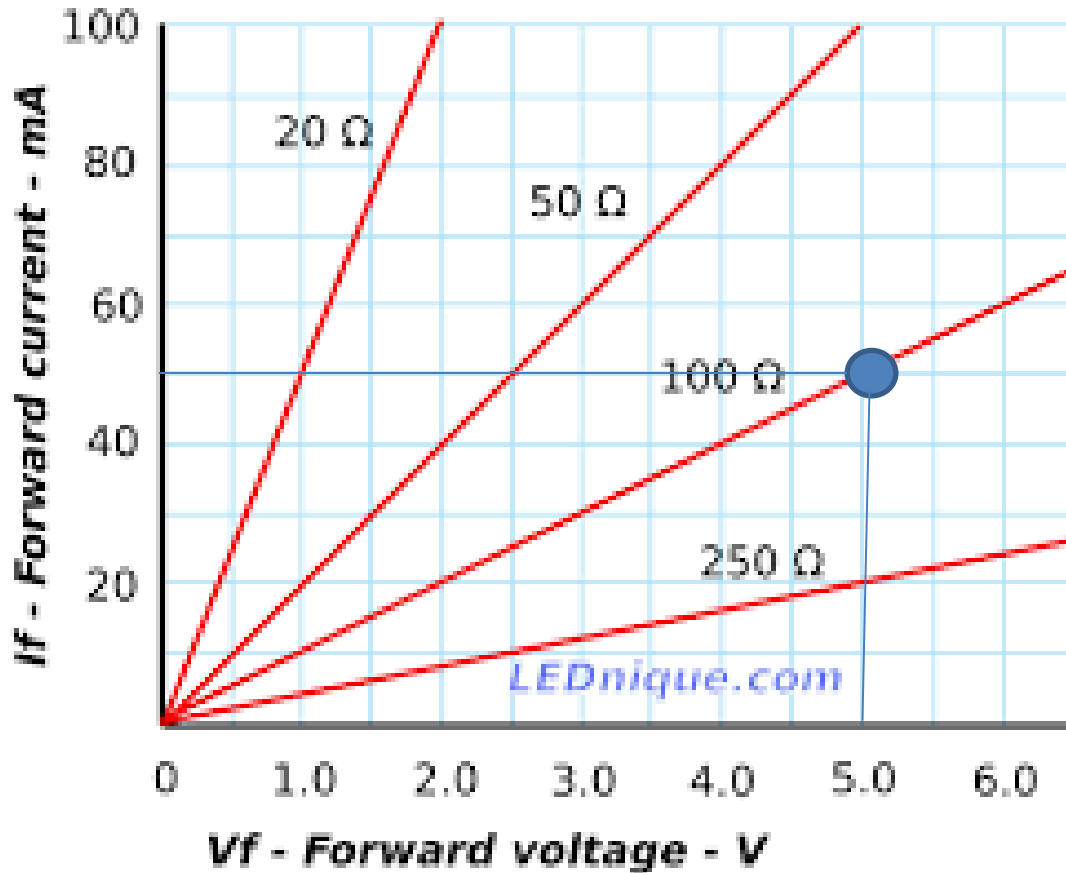
3ª faixa (multiplicador): VERMELHO = x100

4ª faixa (tolerância): DOURADO: 5%

$10 \times 100 = 1000$ ohms

Resistor de 1000 Ohms com 5% de tolerância

Curva tensão vs. corrente de resistor



$$V = RI$$

$$I = V / R$$

$$R = \Delta V / \Delta I$$

$$1 / R = \Delta I / \Delta V$$

Usos do resistor

- Limitação de corrente
- Dissipação de potência (eletricidade)
- Polarização de circuito (eletrônica)

Eletricidade: aplicações de potência ($I > 1 \text{ A}$)

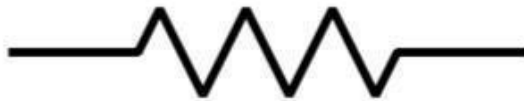
Tecnologia de energia


Eletrônica: aplicações de baixa corrente ($I < 1 \text{ A}$)

Tecnologia de informação

Resistor

Símbolos de um resistor



 **IEEE** Institute of Electrical and Electronics Engineers

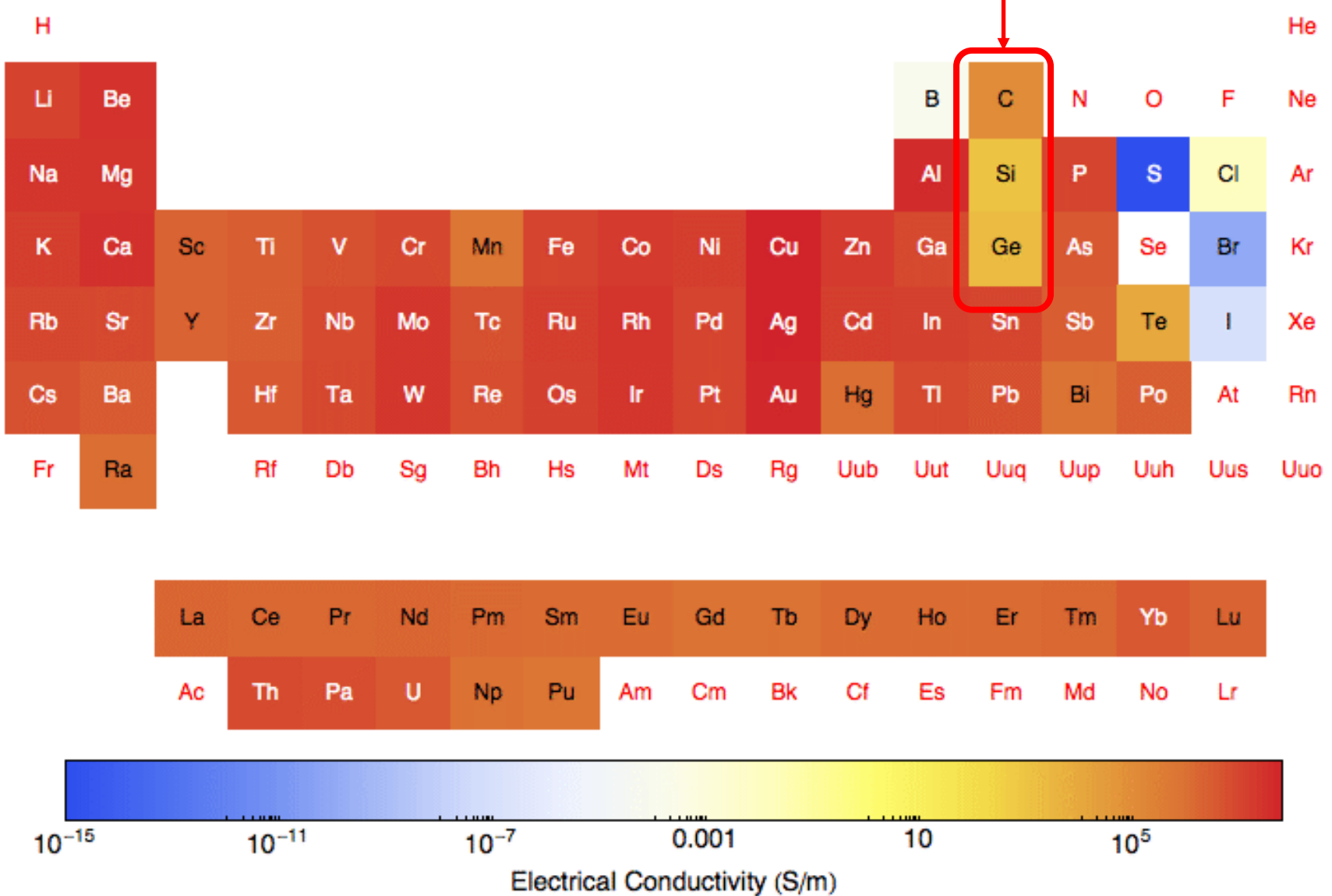


 **IEC** International Electrotechnical Commission

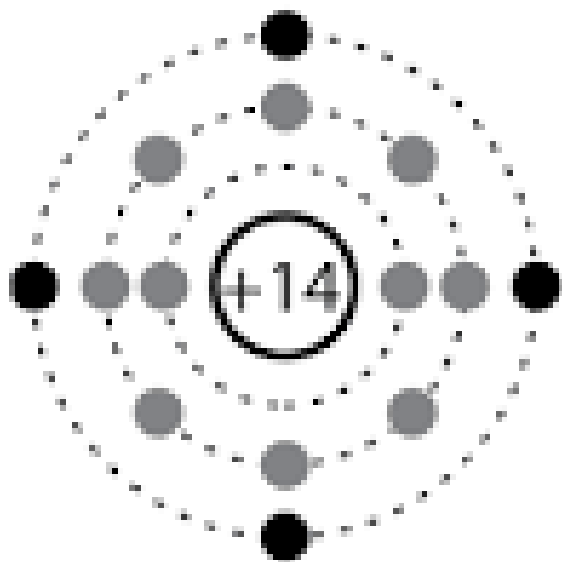


Condutividade elétrica dos elementos

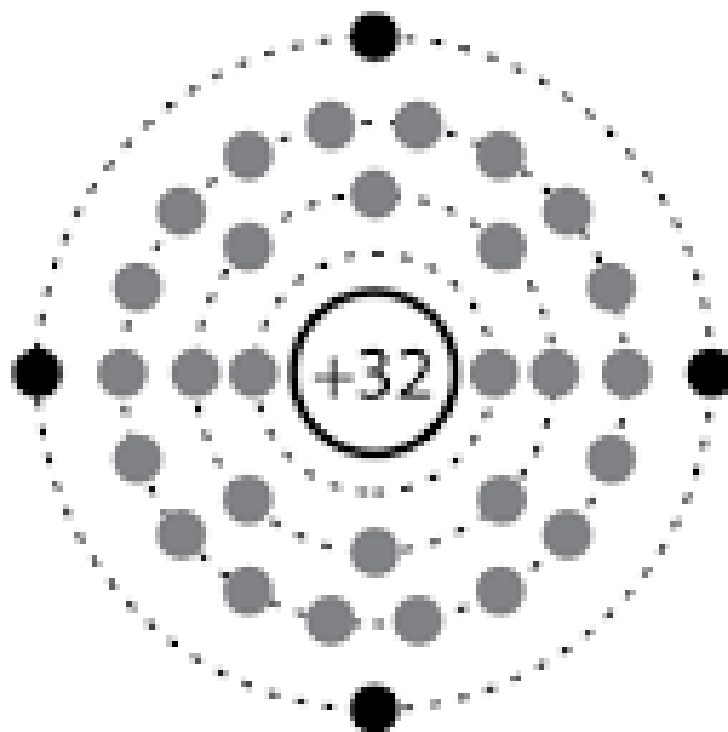
Elementos semicondutores



Ementos semicondutores intrínsecos: silício e germânio

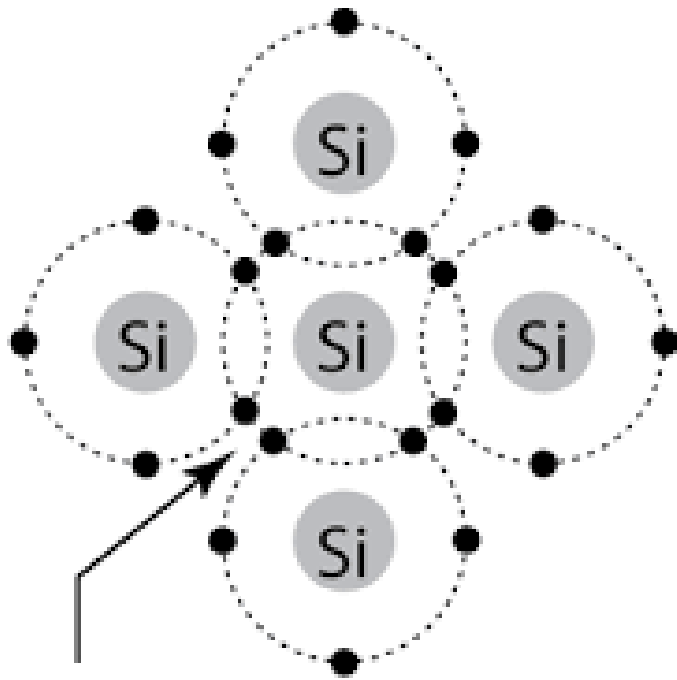


Silicon

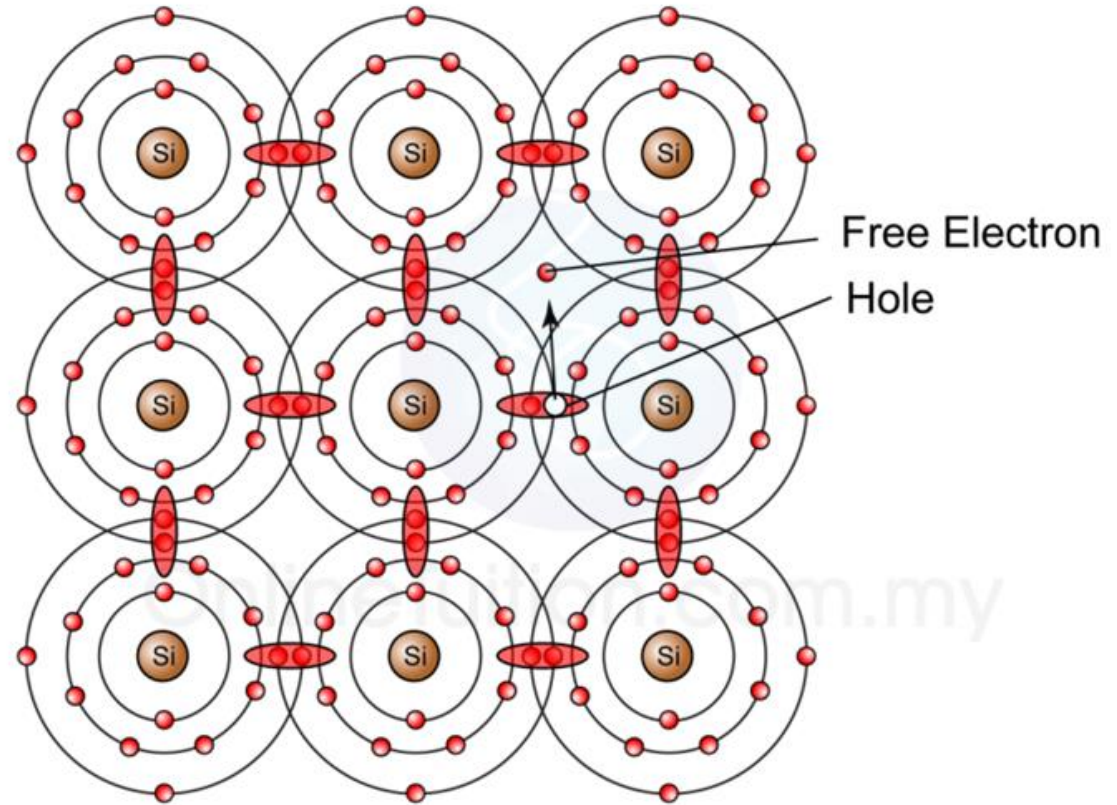


Germanium

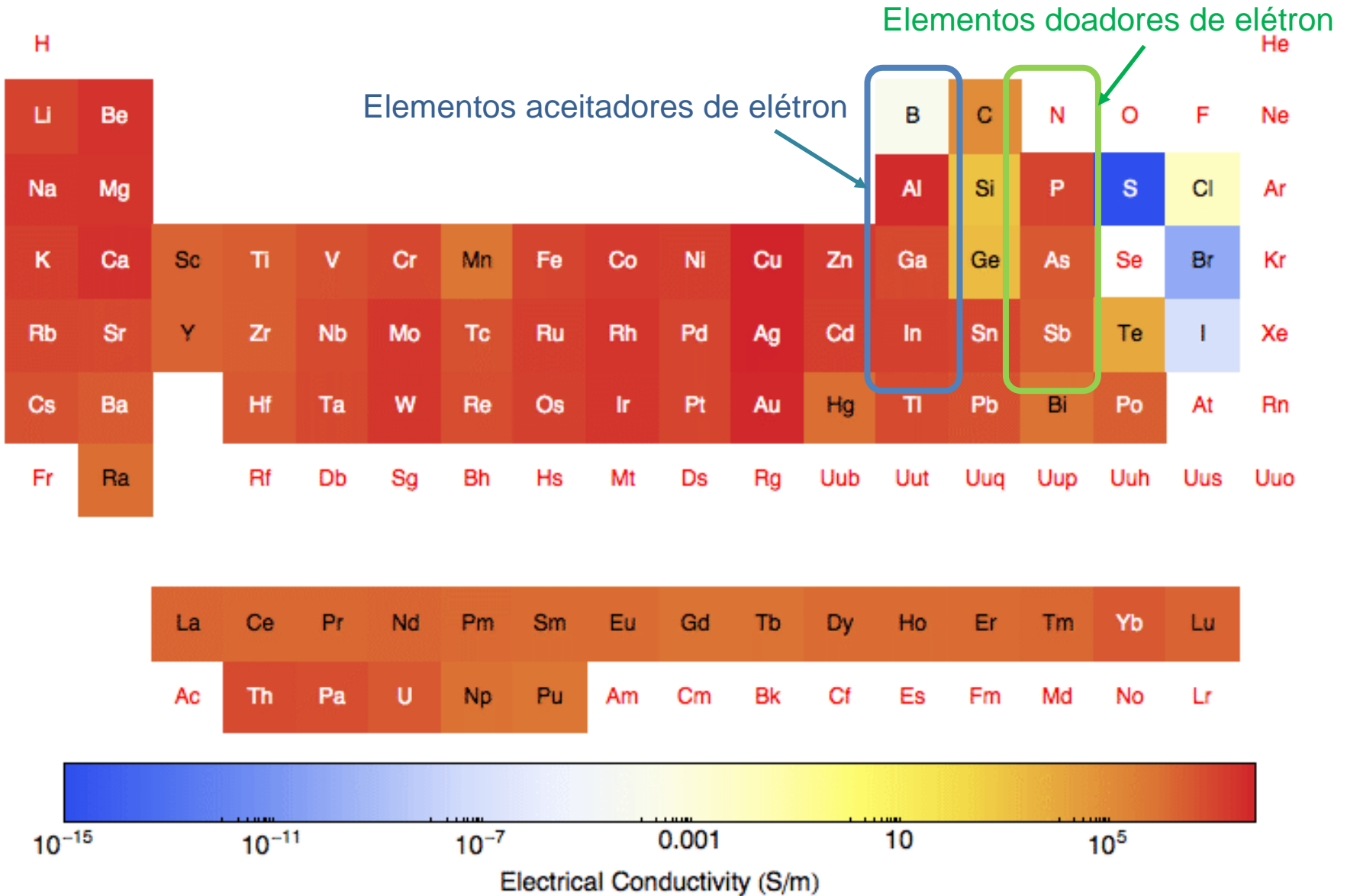
Silício semiconductor intrínseco



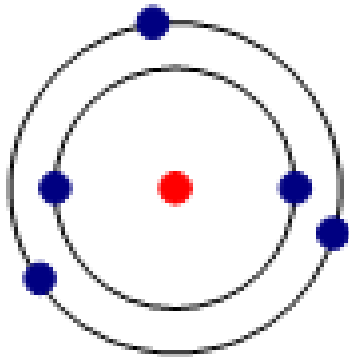
Shared electrons
of a covalent
bond.



Condutividade elétrica dos elementos

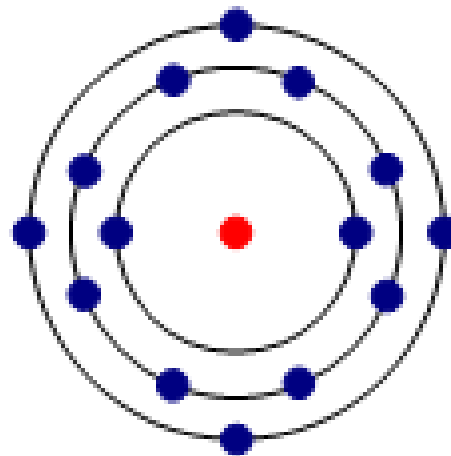


Elementos Boro, Silício e Fósforo



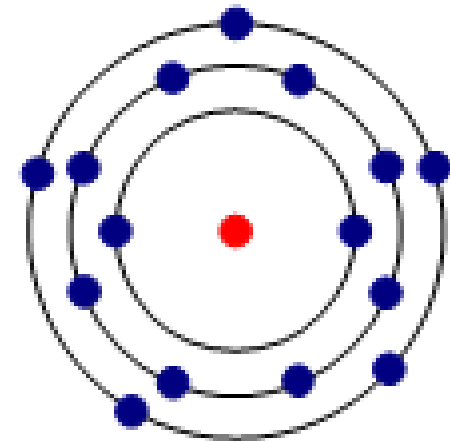
Boron: 5p 6n 5e

3 valence electrons



Silicon: 14p 14n 14e

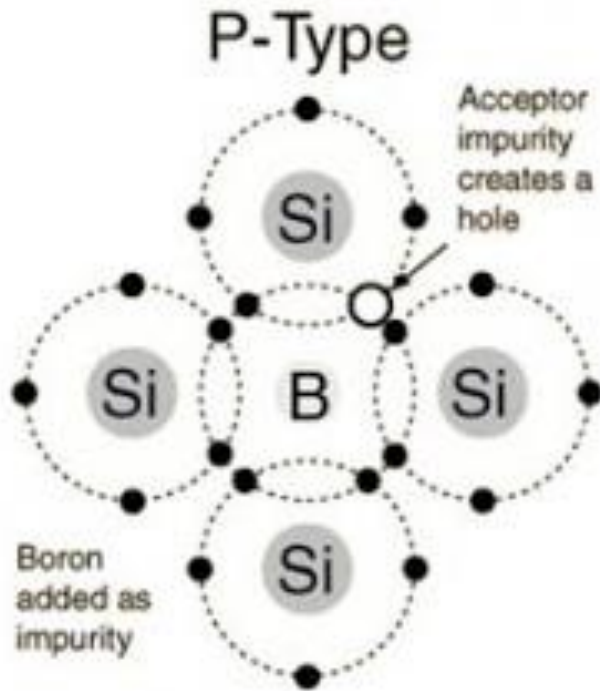
4 valence electrons



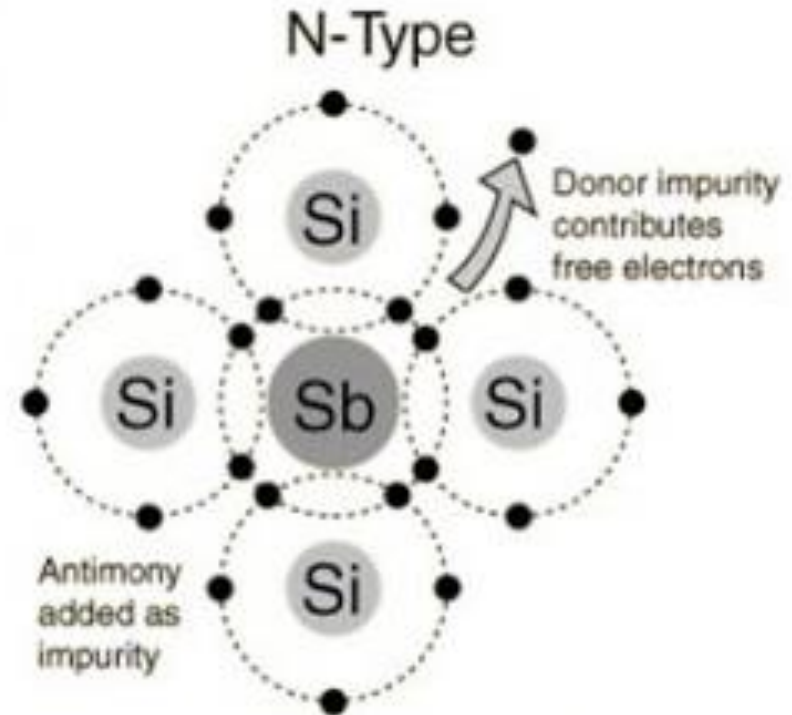
Phosphorus: 15p 15n 15e

5 valence electrons

Silício semiconductor extrínseco

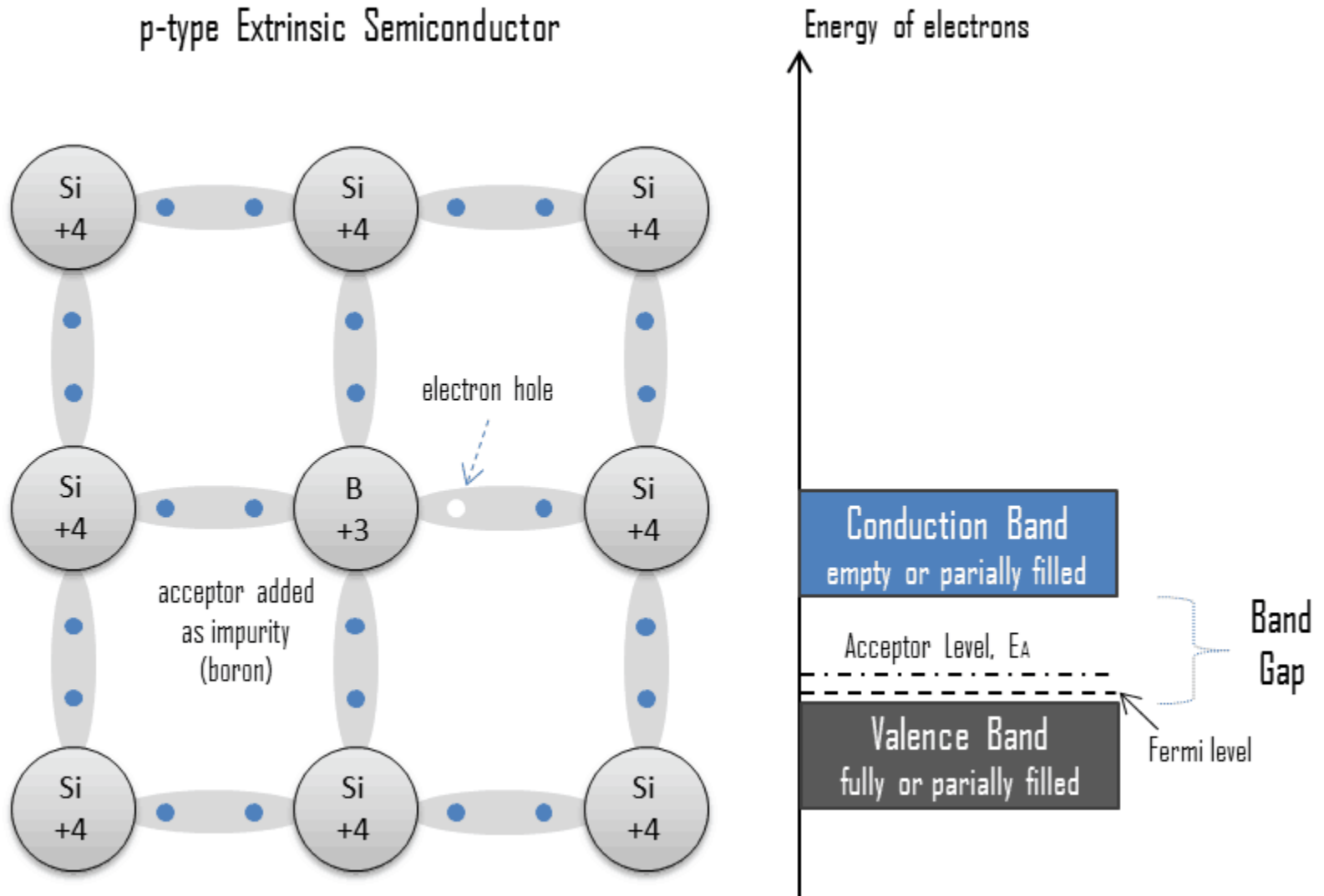


- The P- has a surplus of holes.

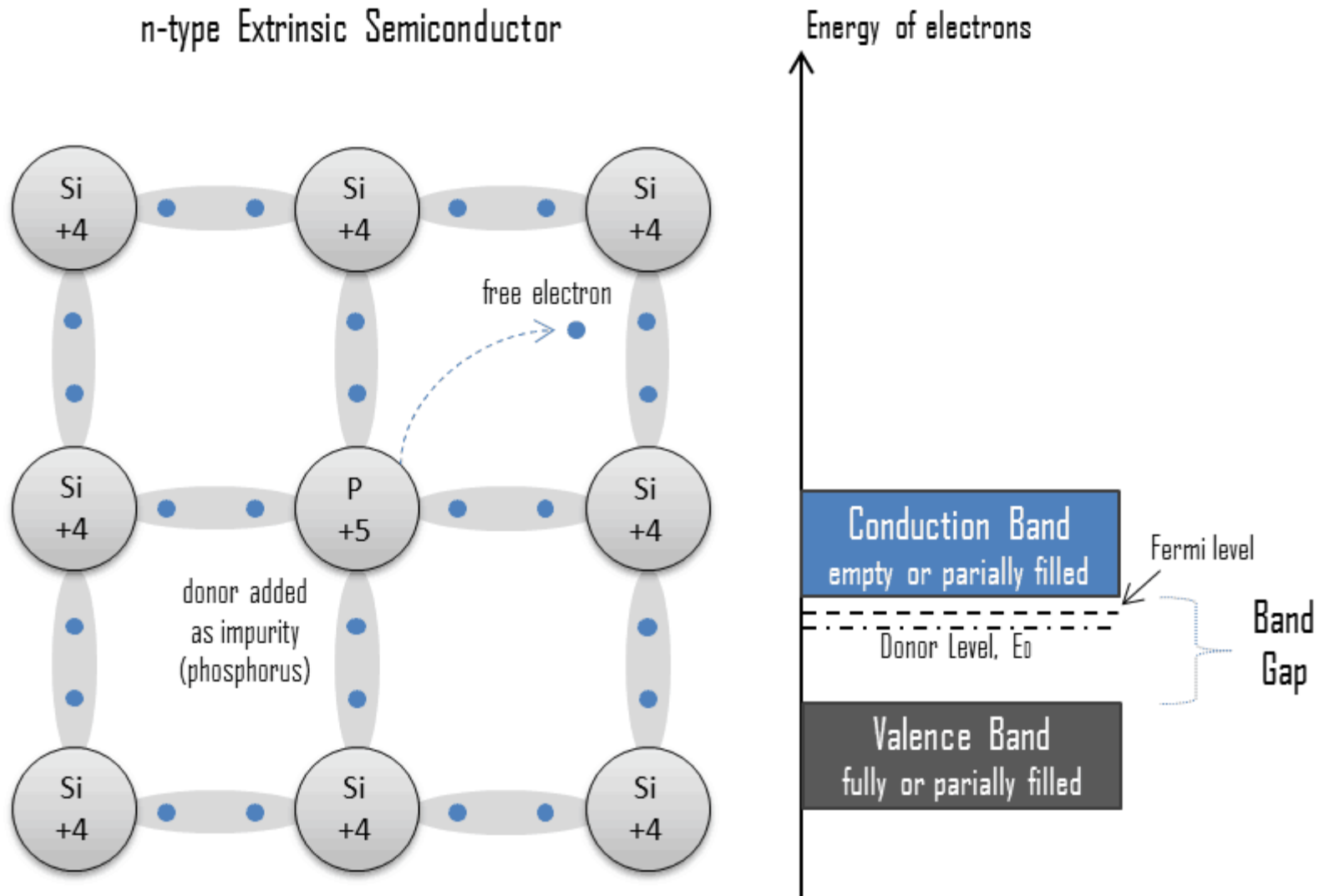


- The N- has a surplus of negative electrons.

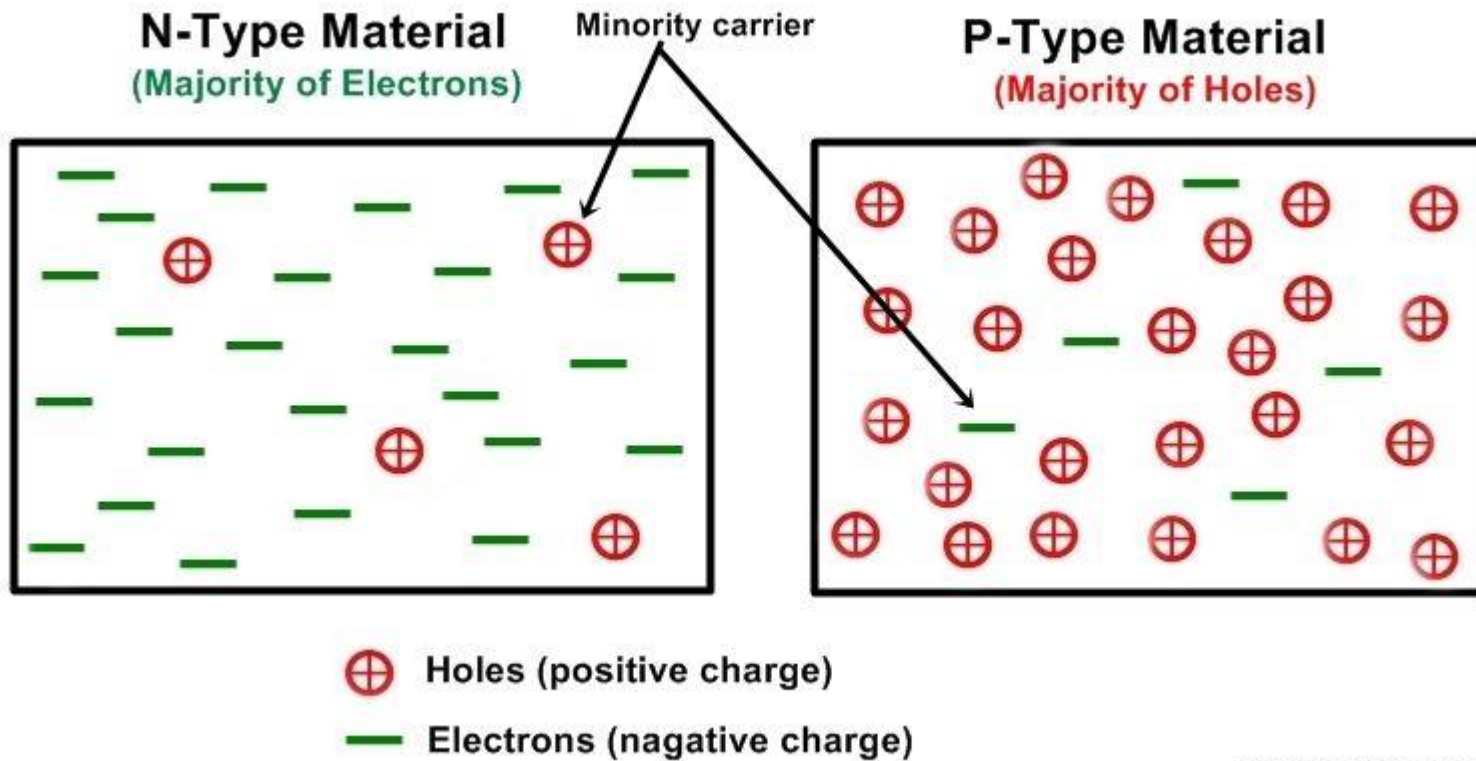
Silício semiconductor extrínseco tipo P



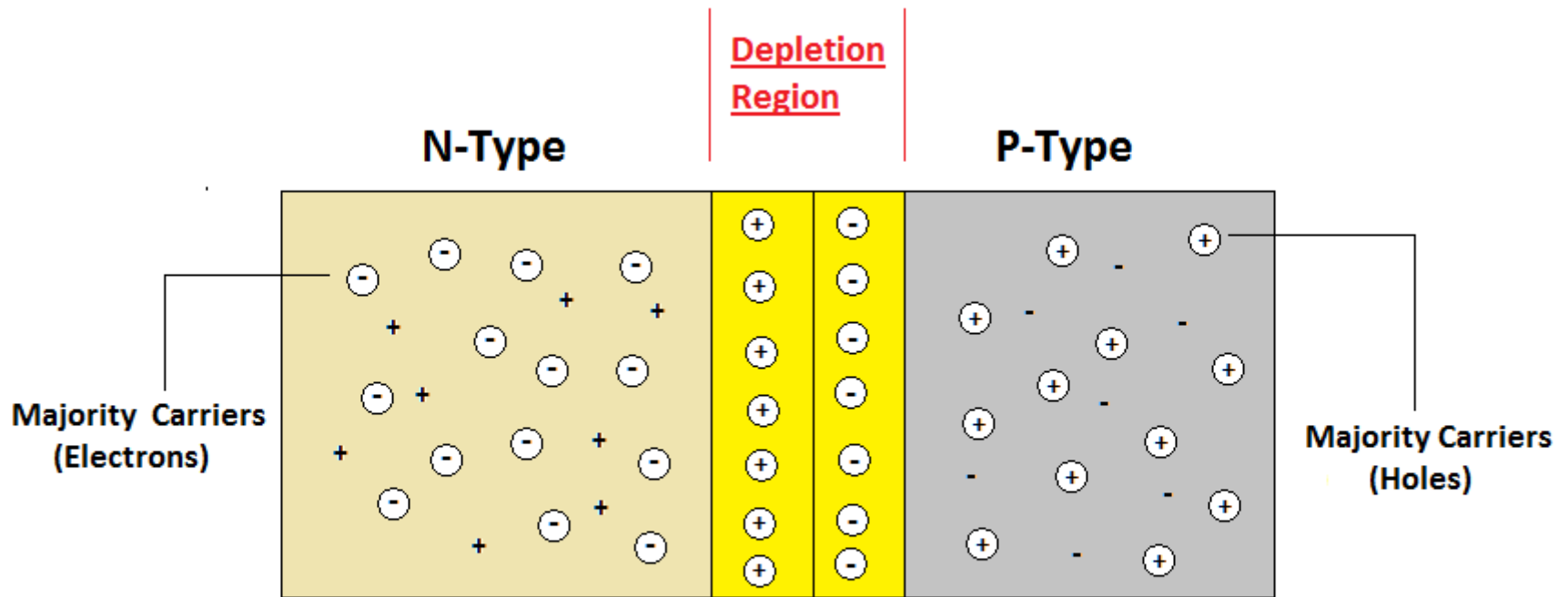
Silício semiconductor extrínseco tipo N



Semicondutores tipo N e P



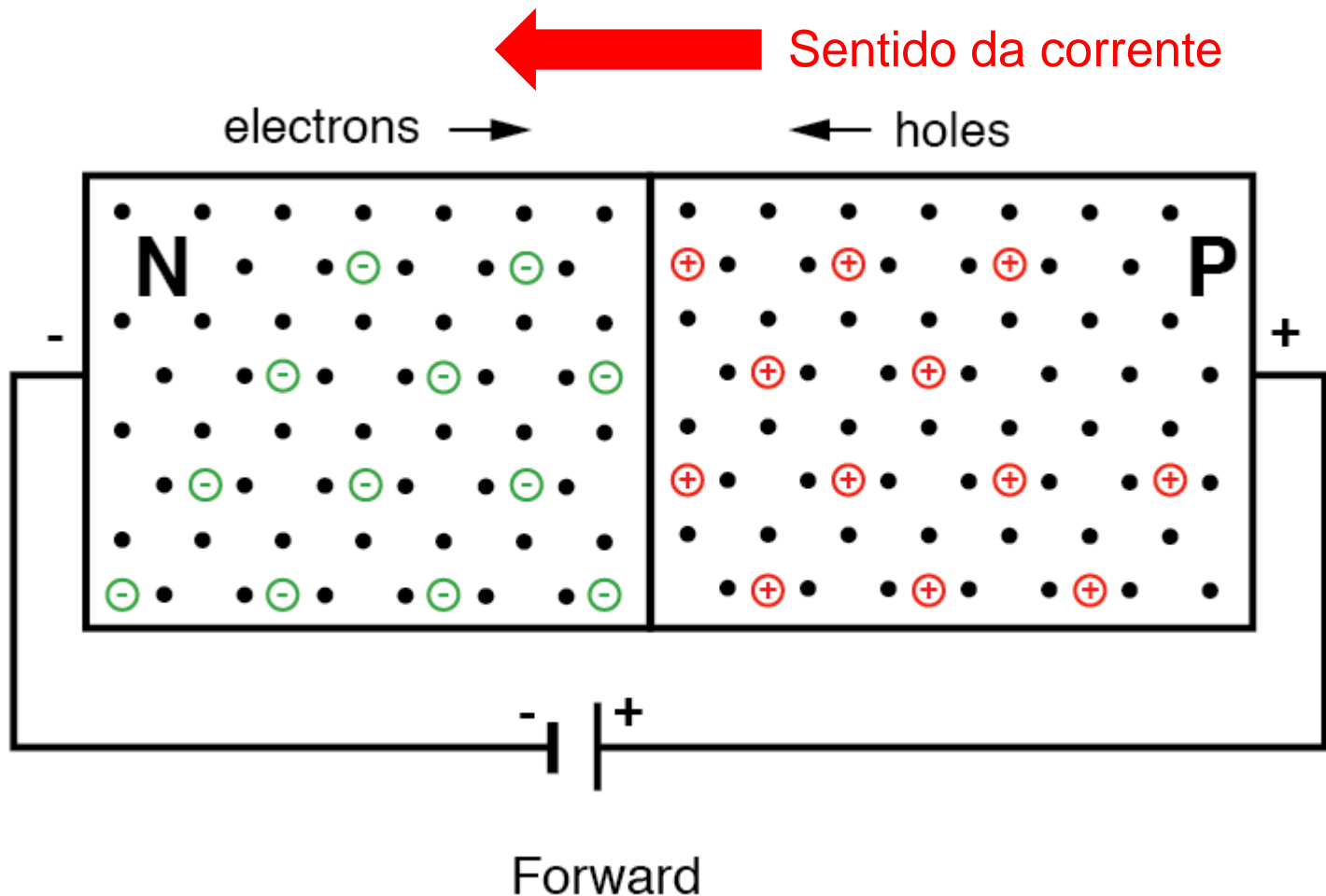
Junção de semicondutores tipo N e P



Silicon Crystal Doped with N-Type & P-Type Impurities

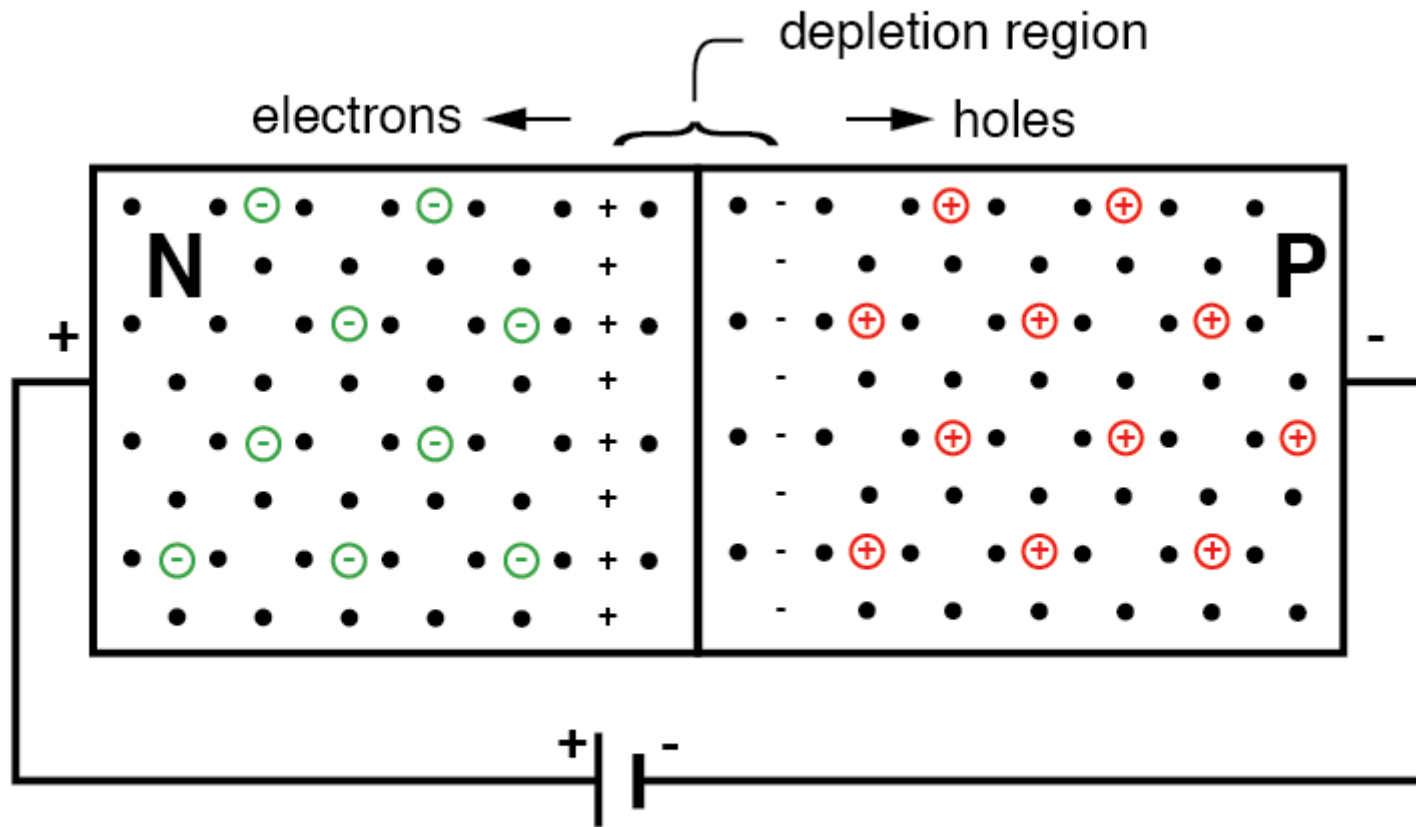
Polarização de diodo de junção PN

Polarização direta: condução de corrente



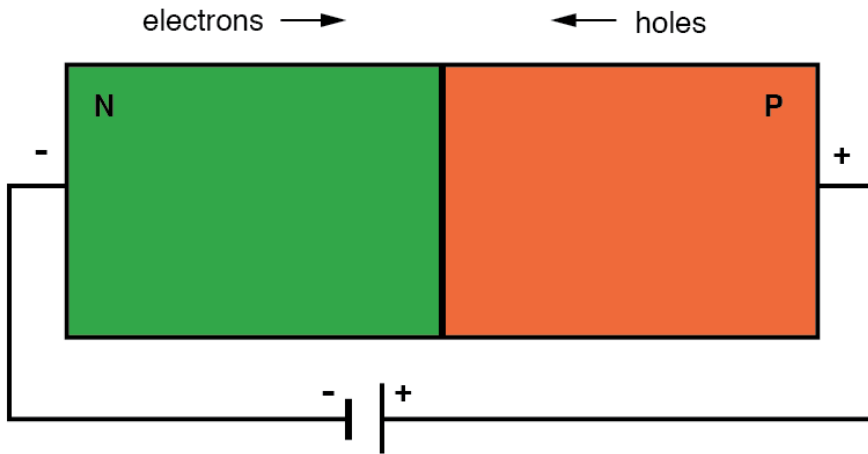
Polarização de diodo de junção PN

Polarização reversa: bloqueio da corrente

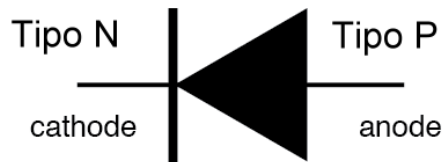


Reverse

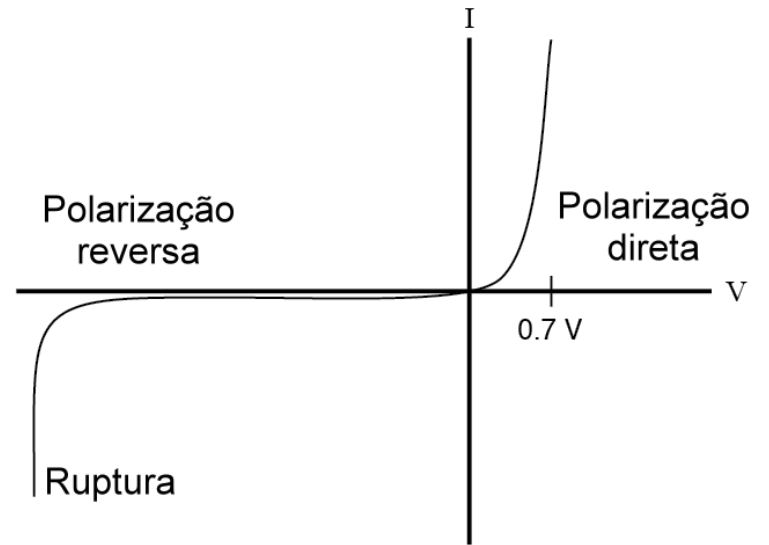
Curva de polarização de diodo de junção PN



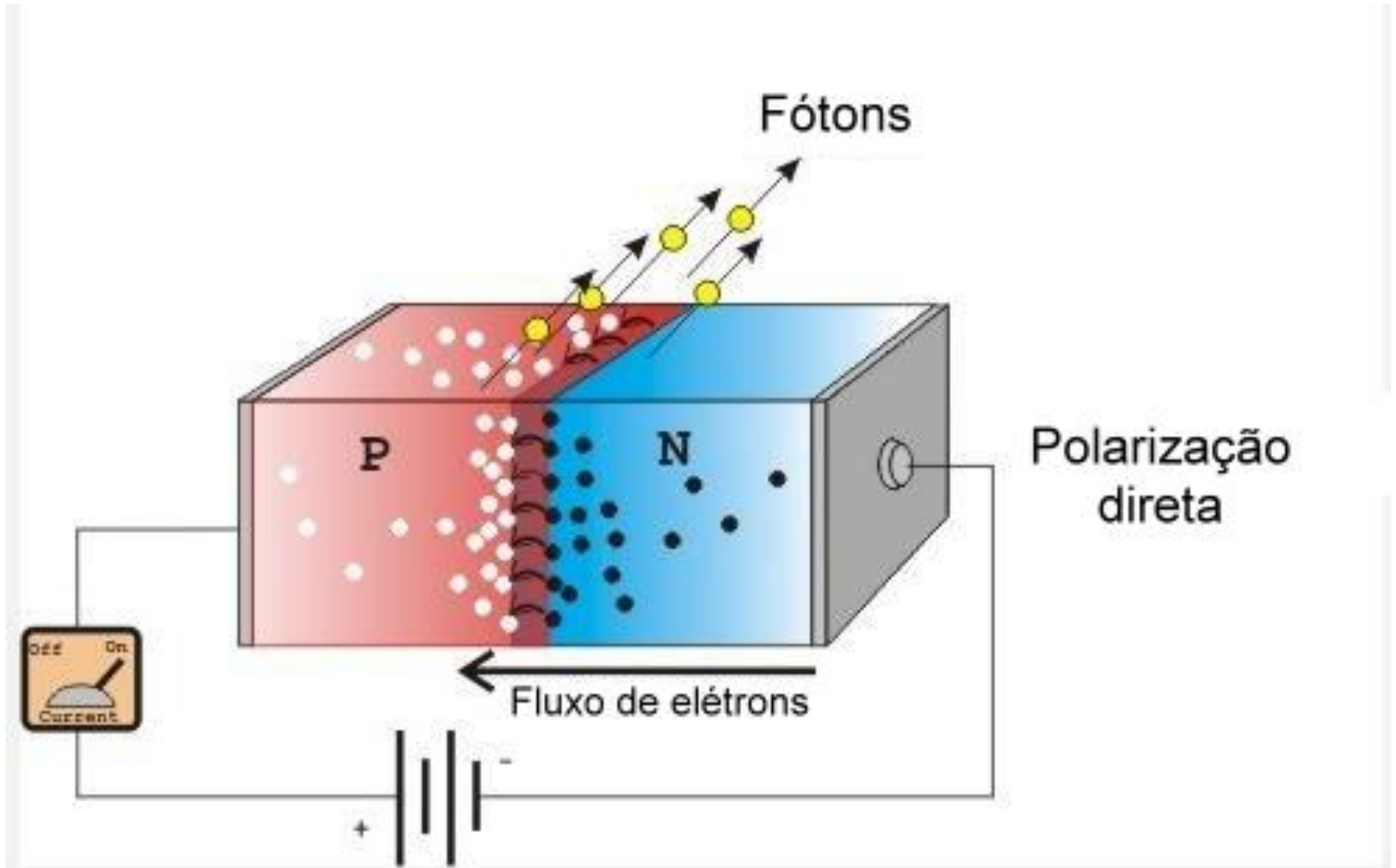
Símbolo



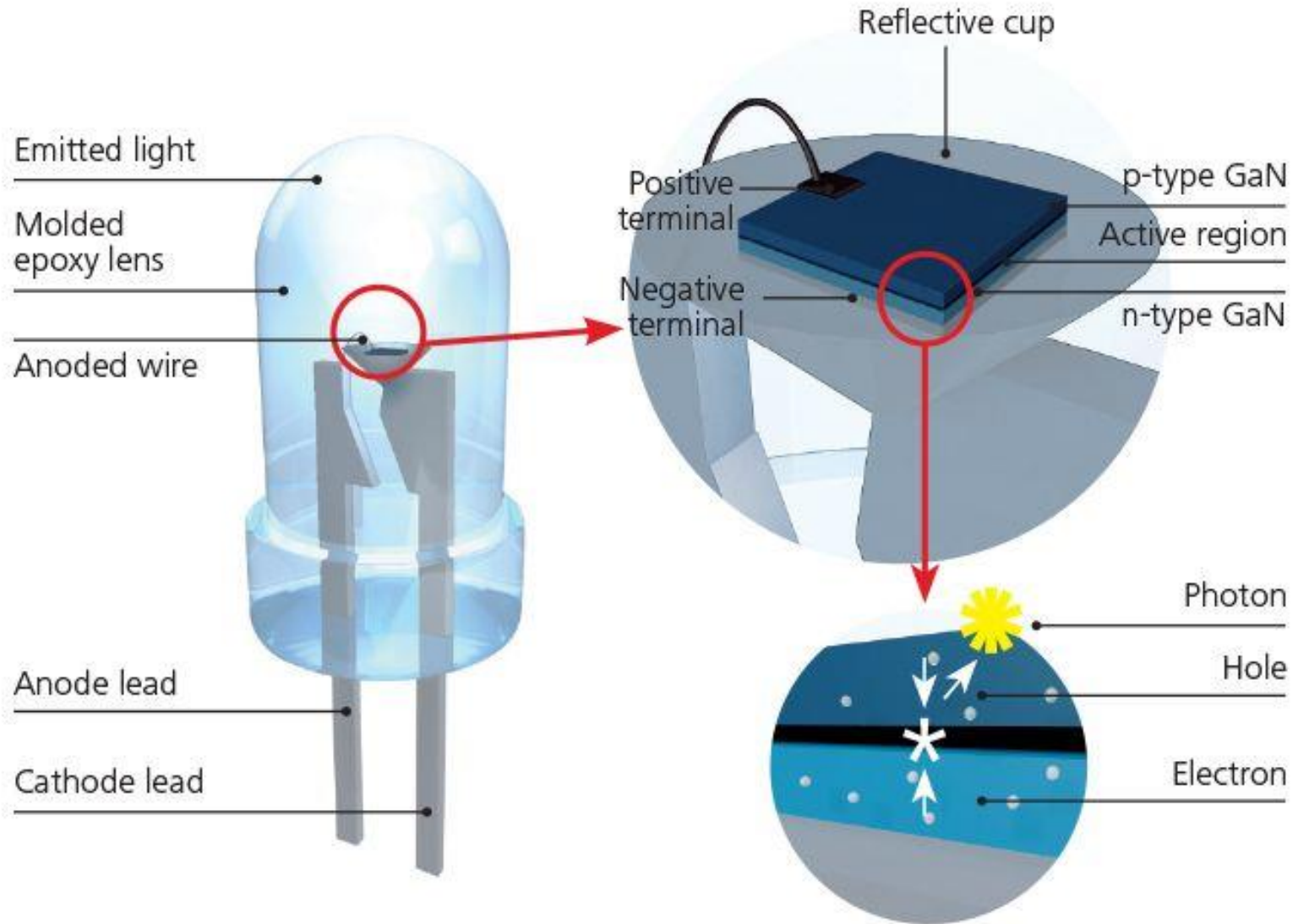
Curva corrente vs. tensão I-V



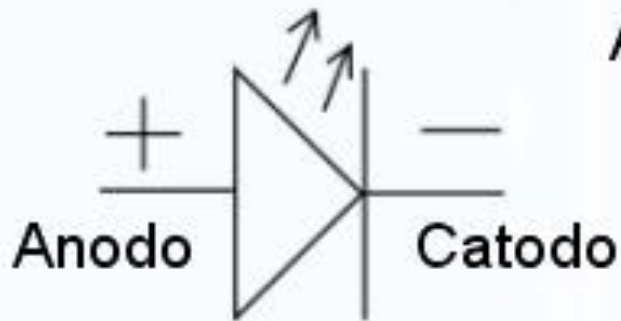
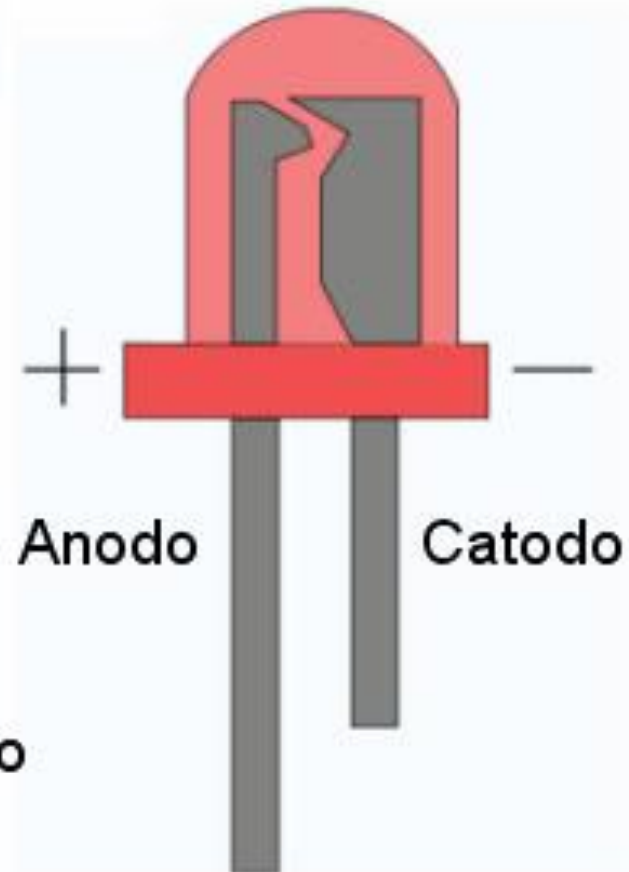
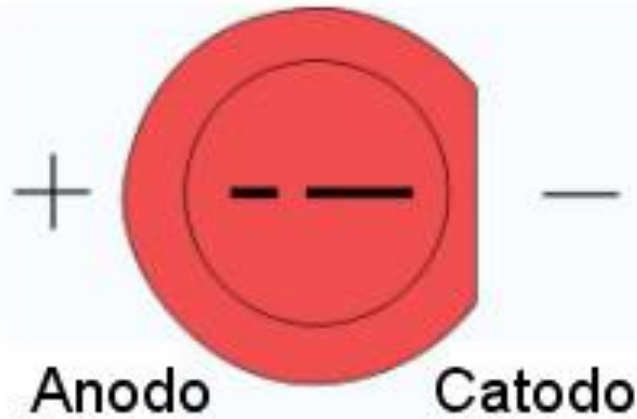
Diodo emissor de luz (LED)



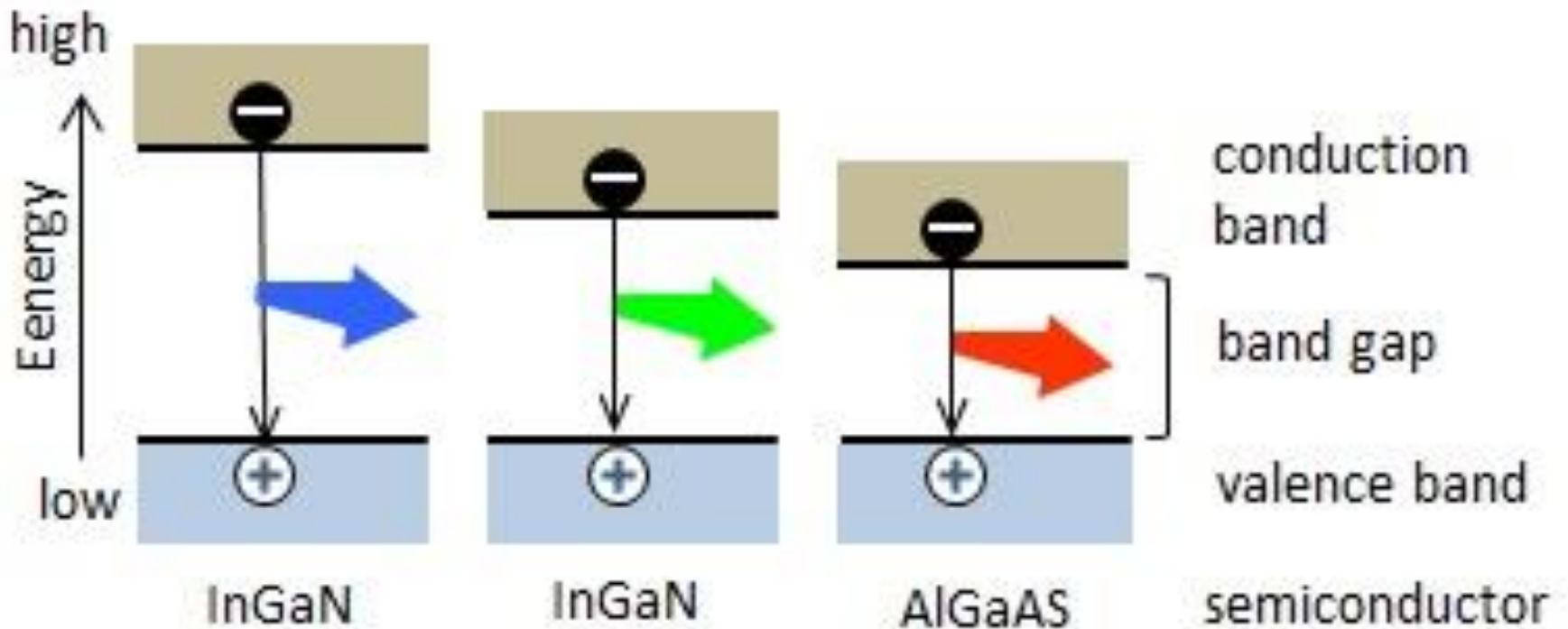
Diodo emissor de luz (LED)



Diodo emissor de luz (LED)



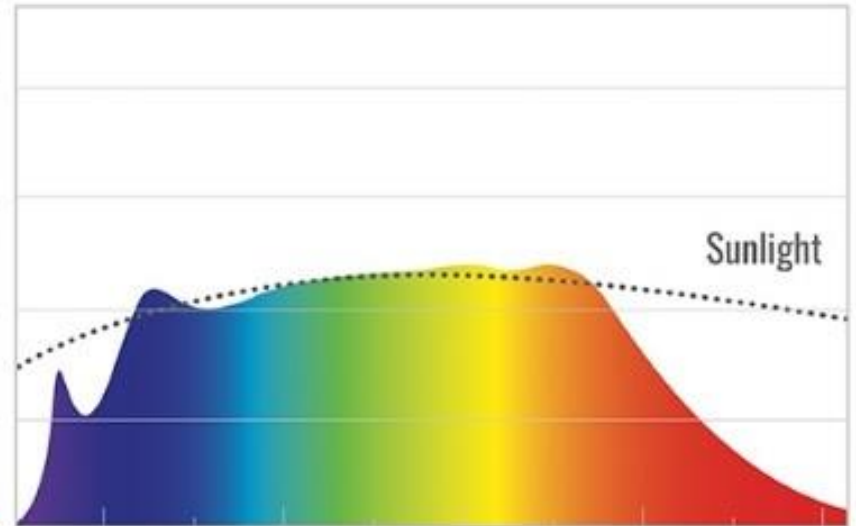
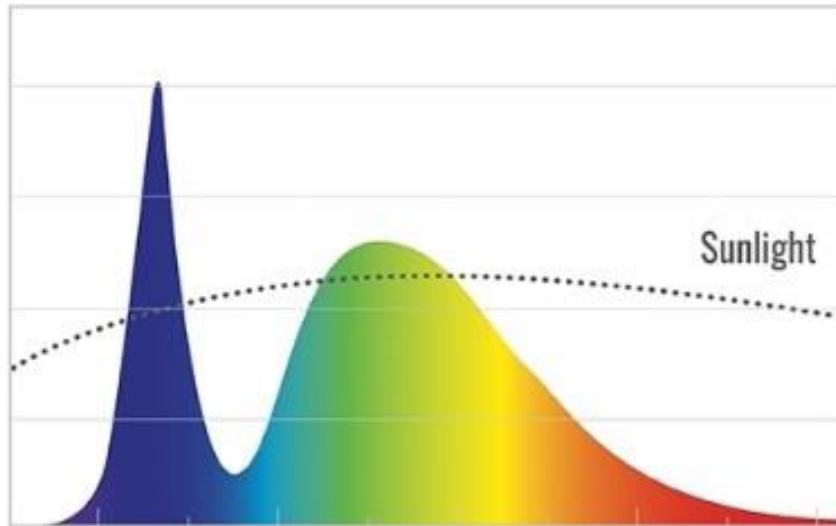
Diodo emissor de luz (LED)



Espectro de emissão do LED

Ordinary LED

SunLike LED
Powered by 

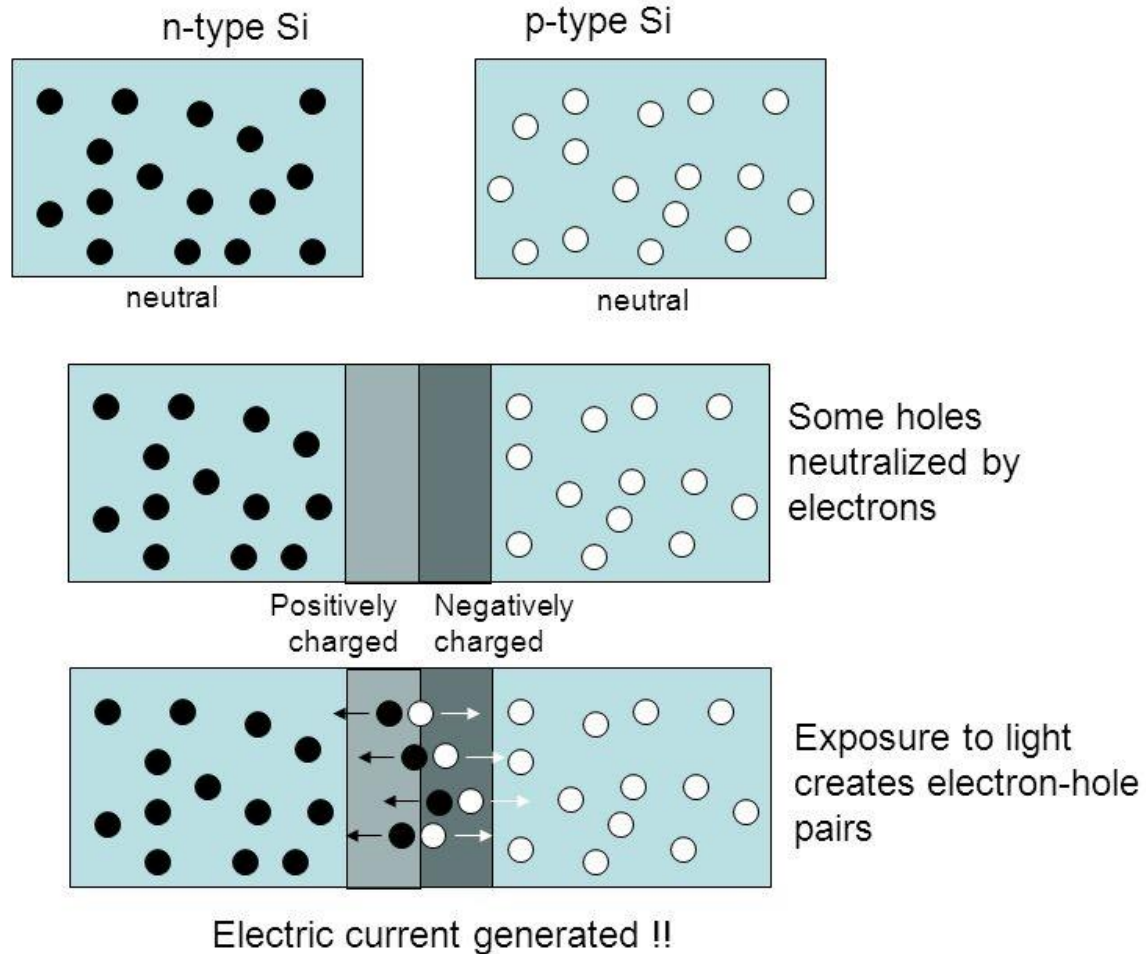


LED branco comum

LED branco de largo espectro

Célula fotovoltaica

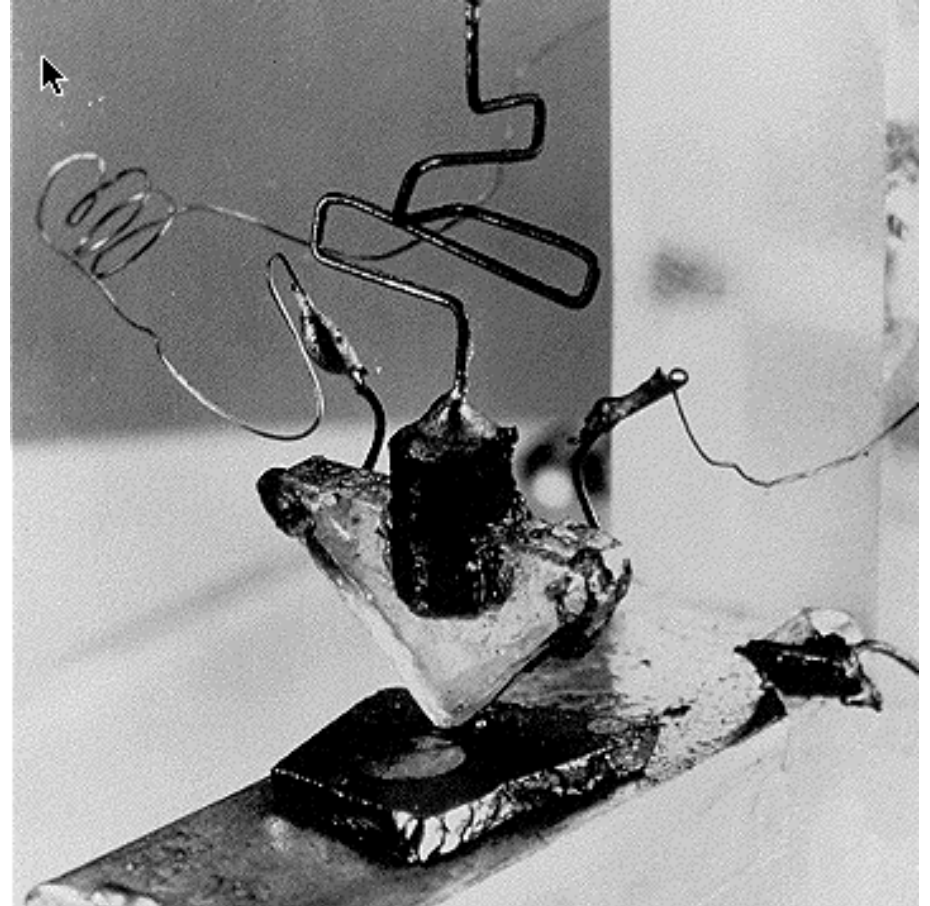
p-n junction solar cell



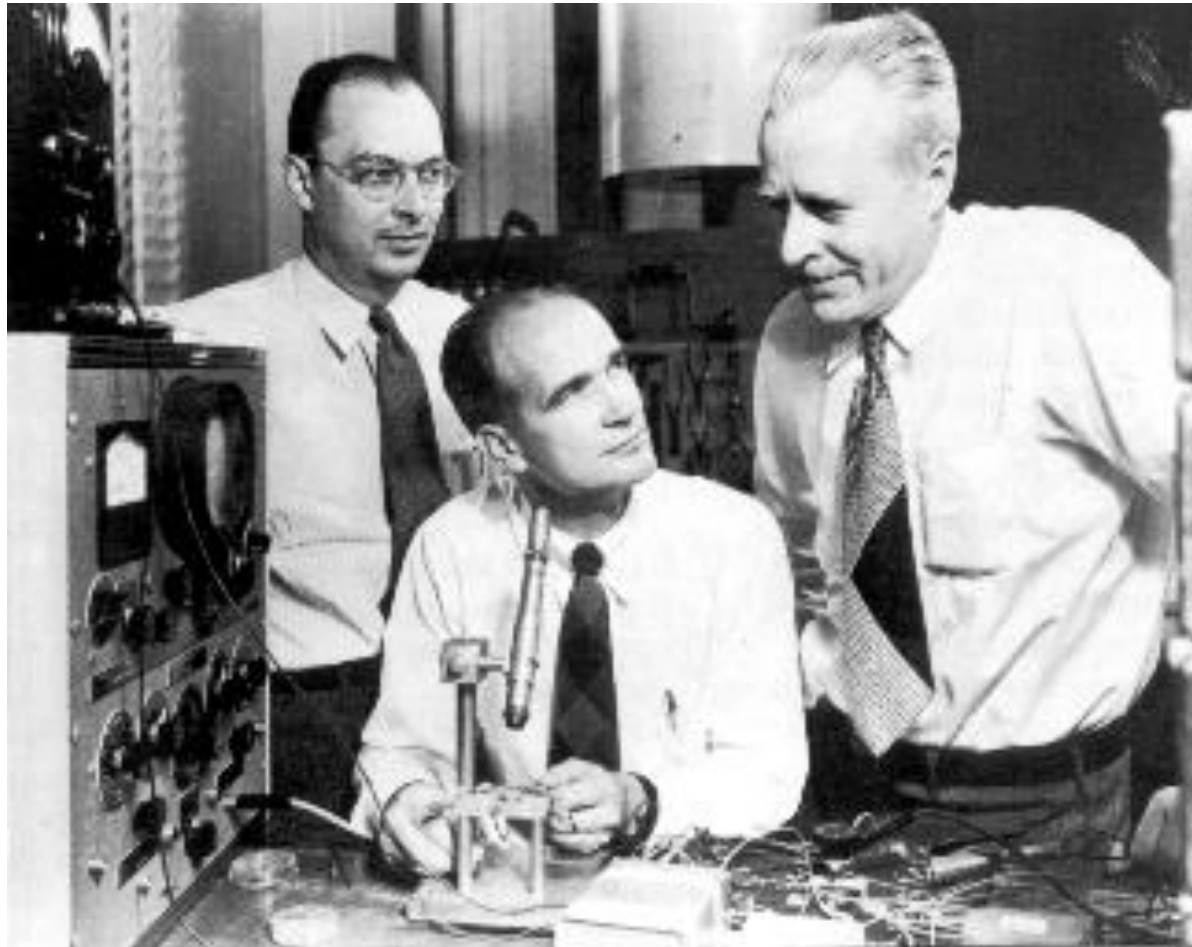
Transistores bipolares

Um pouco de história
Princípio de funcionamento
Tipos: NPN e PNP

Transistor Ponto de Contato



Os inventores do transistor: Bardeen, Shockley e Brattain



Patente do transistor de ponto de contato (Bardeen & Brattain)

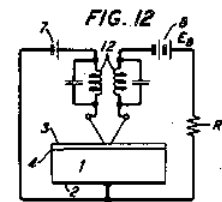
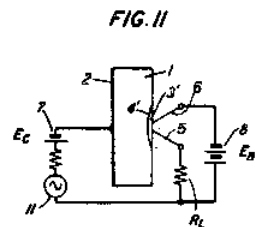
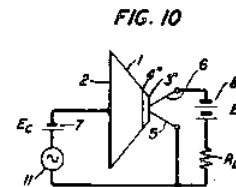
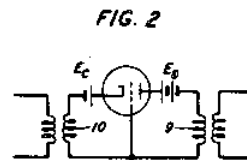
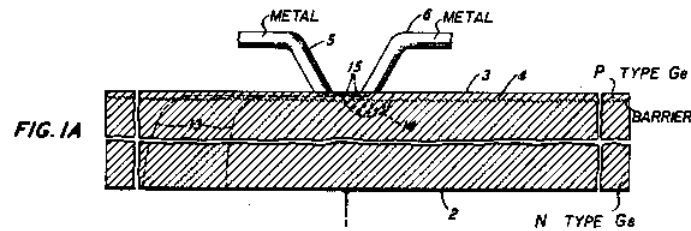
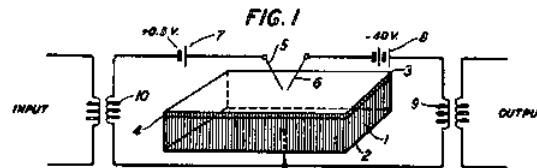
Oct. 3, 1950

J. BARDEEN ET AL
THREE-ELECTRODE CIRCUIT ELEMENT UTILIZING
SEMICONDUCTIVE MATERIALS

2,524,035

Filed June 17, 1948

3 Sheets-Sheet 1



INVENTORS: J. BARDEEN
W. H. BRATTAIN
BY Harry C. Hart
ATTORNEY

Patente do transistor sanduíche (Shockley)

Sept. 25, 1951

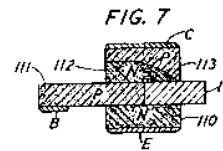
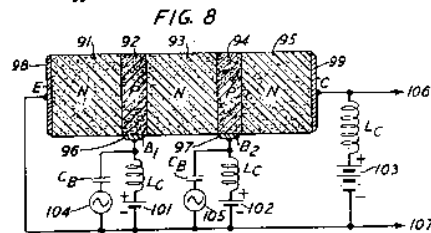
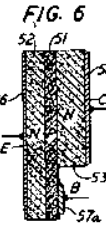
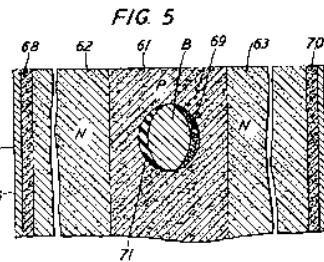
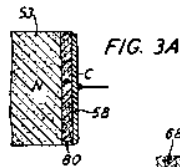
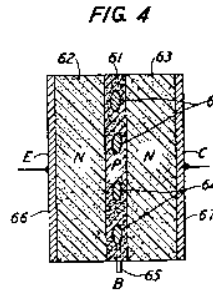
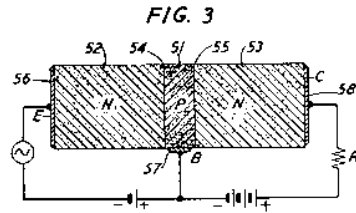
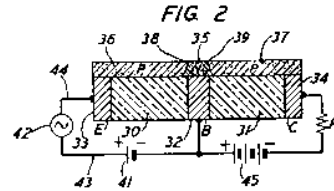
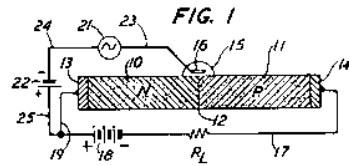
W. SHOCKLEY

2,569,347

CIRCUIT ELEMENT UTILIZING SEMICONDUCTIVE MATERIAL

Filed June 26, 1948

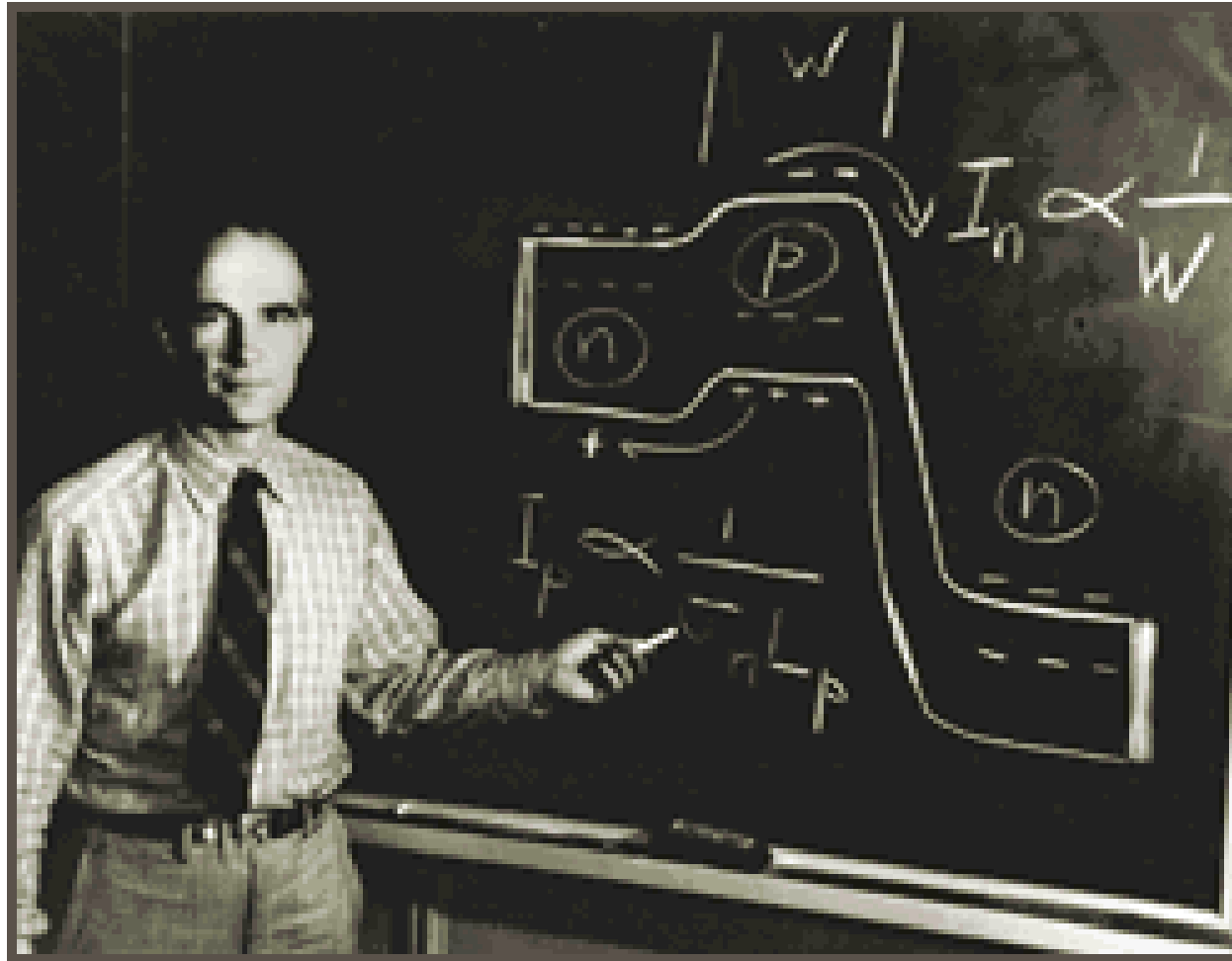
3 Sheets-Sheet 1



INVENTOR
W. SHOCKLEY
BY *[Signature]*

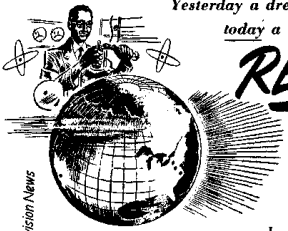
ATTORNEY

O “pai” do Vale do Silício: William Shockley



Propaganda

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today a
REALITY!



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the electronic world
has waited for...
here at last...
brought to you first by **FEDERATED!**

June, 1952
Radio & Television News

JUNCTION TYPE (No. RD 2517)

TRANSISTORS

(crystal amplifiers)

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Allentown, Penna.
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Propaganda

TAKE THIS
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**A RAYTHEON
TRANSISTOR**

This is a mechanical sample
only - an electrical "reject".
It will not work.

RAYTHEON

*Raytheon . . . Electronic Miracle
Maker for Over a Quarter of
a Century . . . Presents You with
This Sample of a Transistor.*

Here's WHY it's wonderful:

- ◆ Never wears out.
- ◆ Can't burn out.
- ◆ Won't deteriorate.
- ◆ Impervious to moisture.
- ◆ Resistant to jars and jolts.
- ◆ Uses almost no current.
- ◆ Gives greater undistorted volume.

Here's what it means to YOU . . .

Miracle Radio!
NO TUBES!



Nothing to Plug in!
Over 500 Hours on Flashlight Batteries!
**Speaker Grilles Front and Back for 360°
of Rich "Live" Sound!**

Tiny transistors replace bulky radio tubes — withstand hard knocks — use almost no current. Far more convenient and actually costs less to operate than conventional AC-DC radio sets. Genuine leather case. Luggage brass control knobs. Long shoulder strap or short carrying handle.

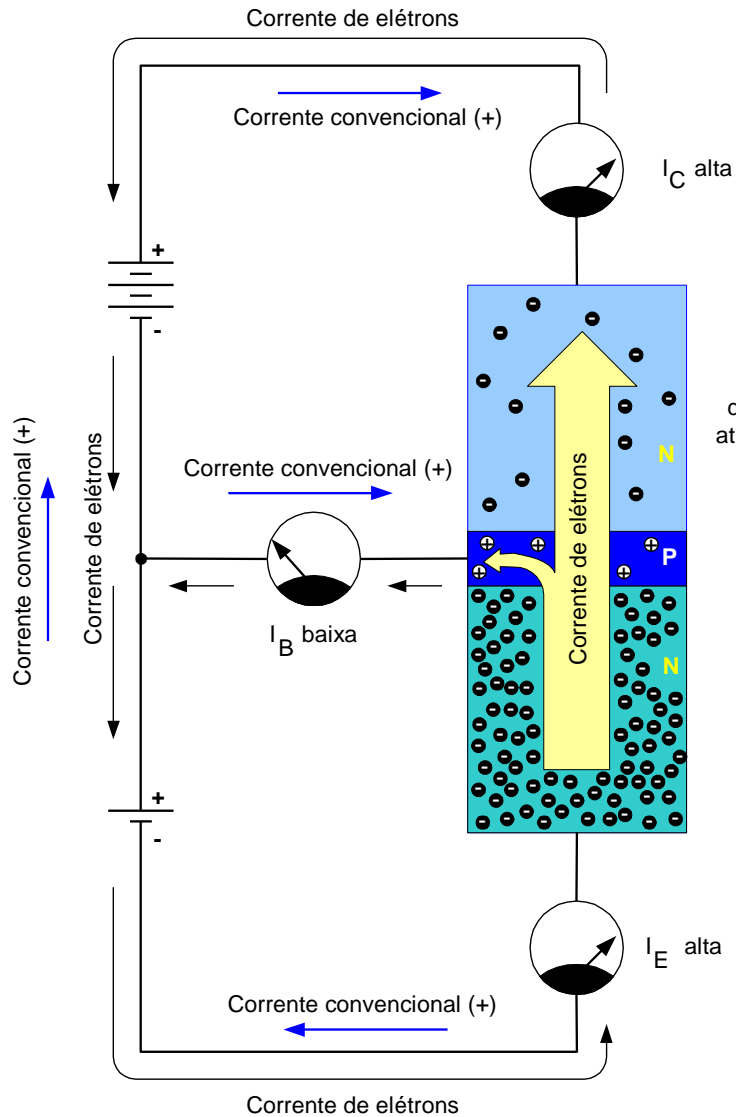
RAYTHEON *Transistor*
RADIO
world's largest producers of transistors

Transistor bipolar

Princípio de funcionamento:

Os portadores majoritários bem como os portadores minoritários participam do processo de condução elétrica, daí o nome transistor bipolar.

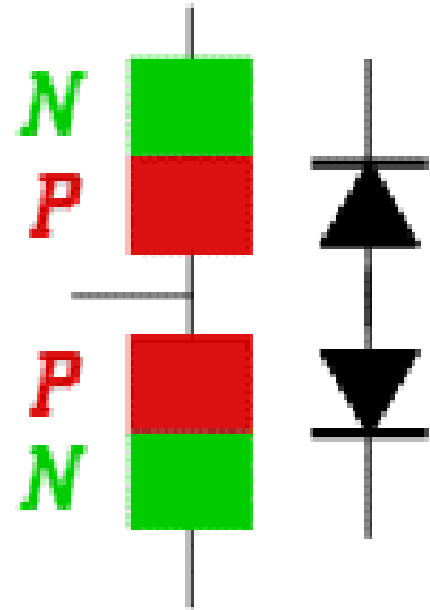
Transistor bipolar NPN



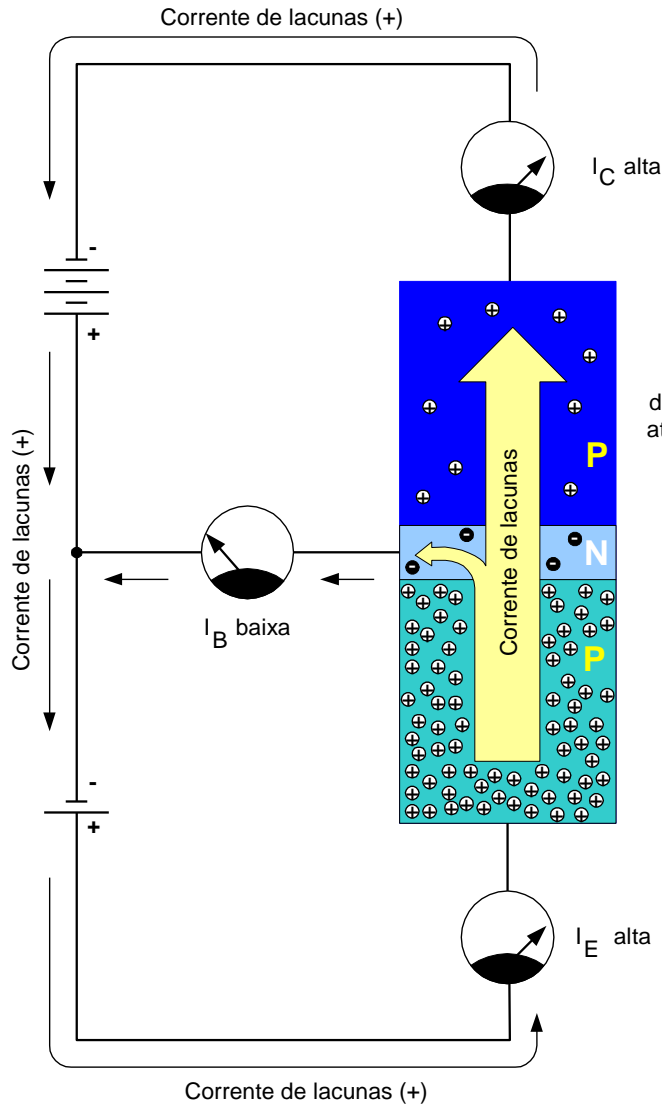
O coletor, levemente dopado, está "positivo" e atrai os elétrons vindos do emissor

A base está pobre de lacunas

O emissor, altamente dopado, está "rico" de elétrons



Transistor bipolar PNP



O coletor, levemente dopado, está "negativo" e atrai as lacunas vindas do emissor

A base está pobre de elétrons

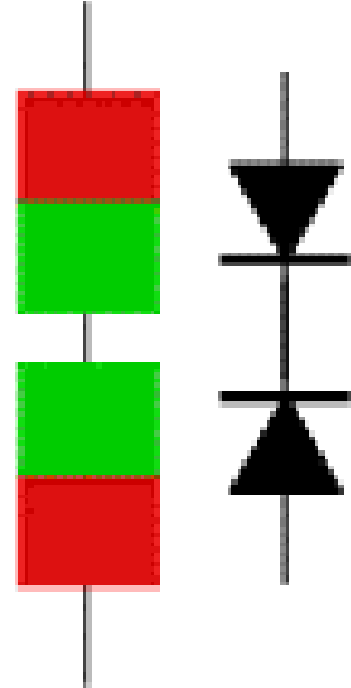
O emissor, altamente dopado, está "rico" de lacunas

P

N

N

P

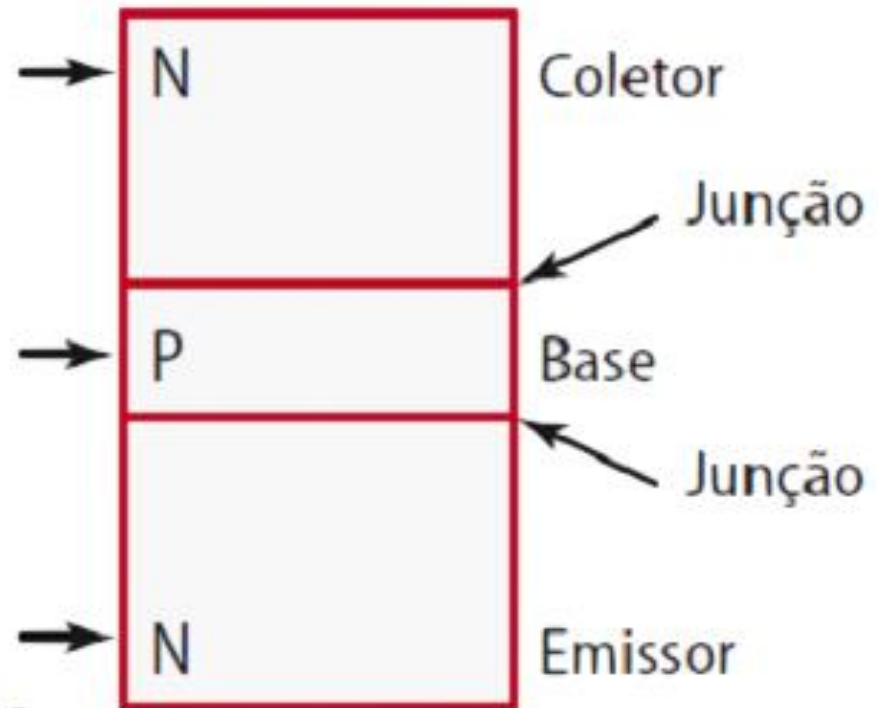


Estrutura de um transistor bipolar NPN

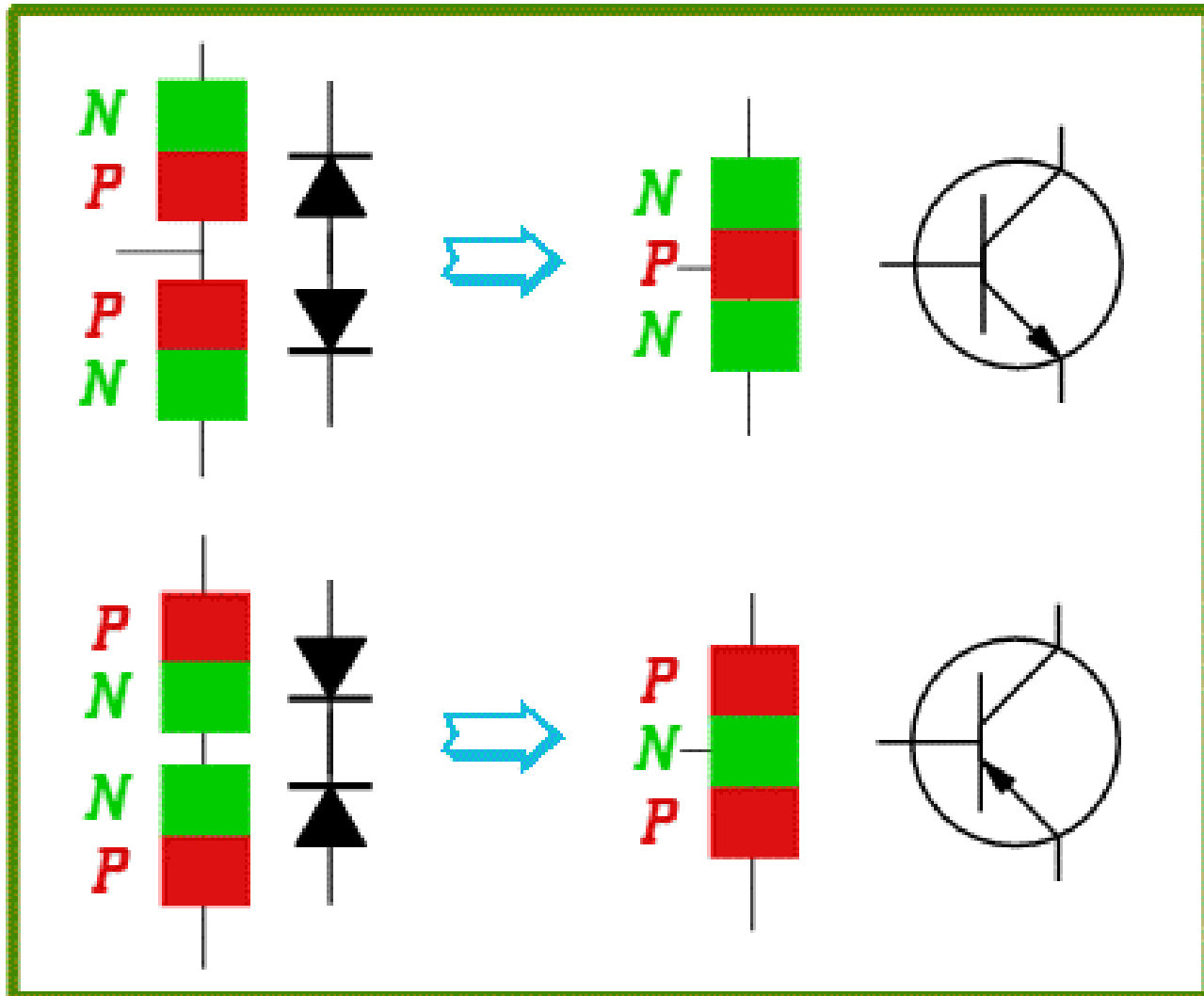
Levemente dopada.
Esta região "coleta" os portadores de corrente

Levemente dopada.
Esta região "controla" o fluxo de corrente

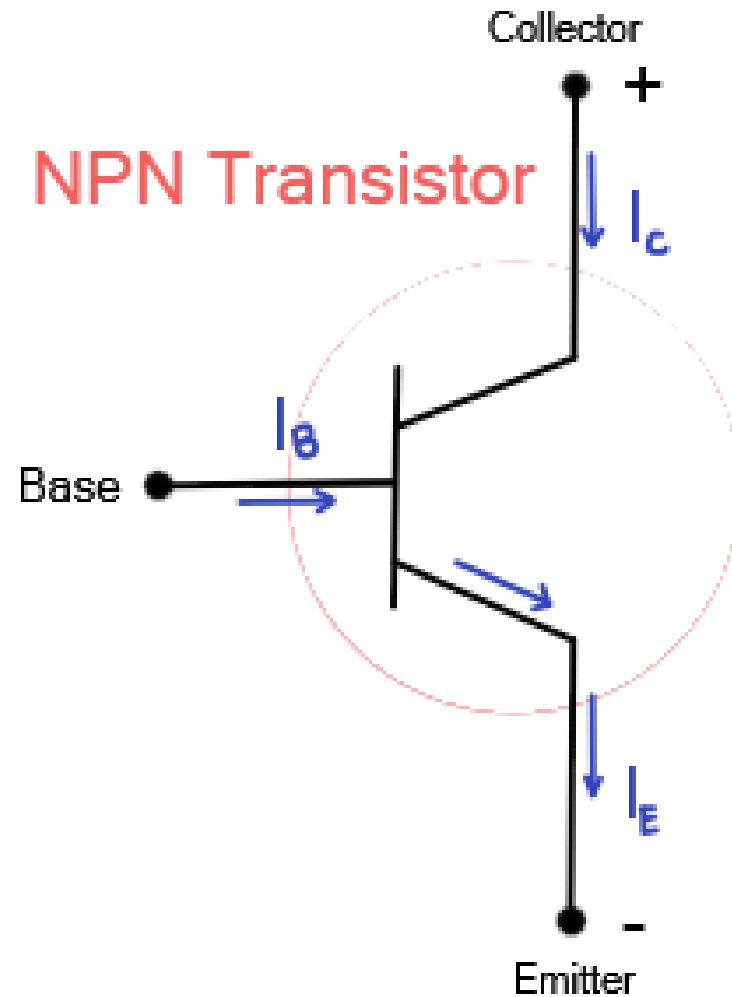
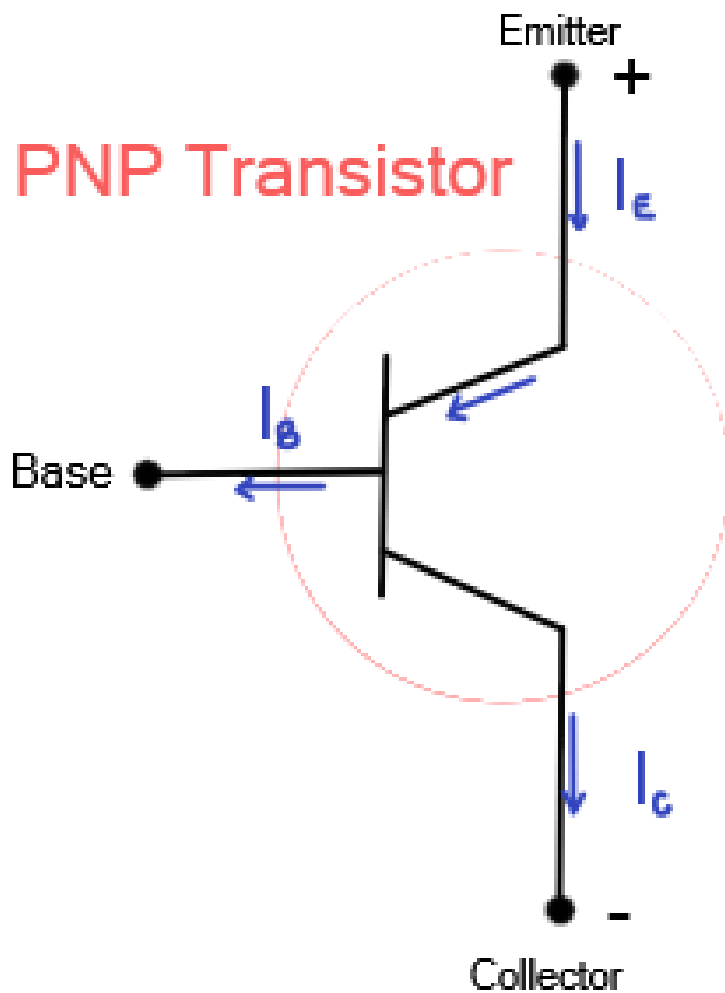
Altamente dopada.
Esta região "emite" os portadores de corrente



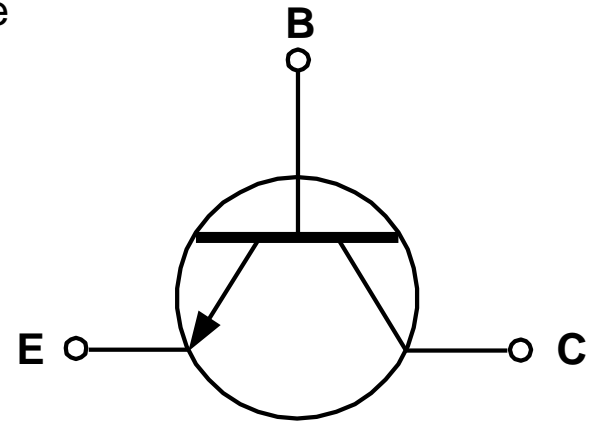
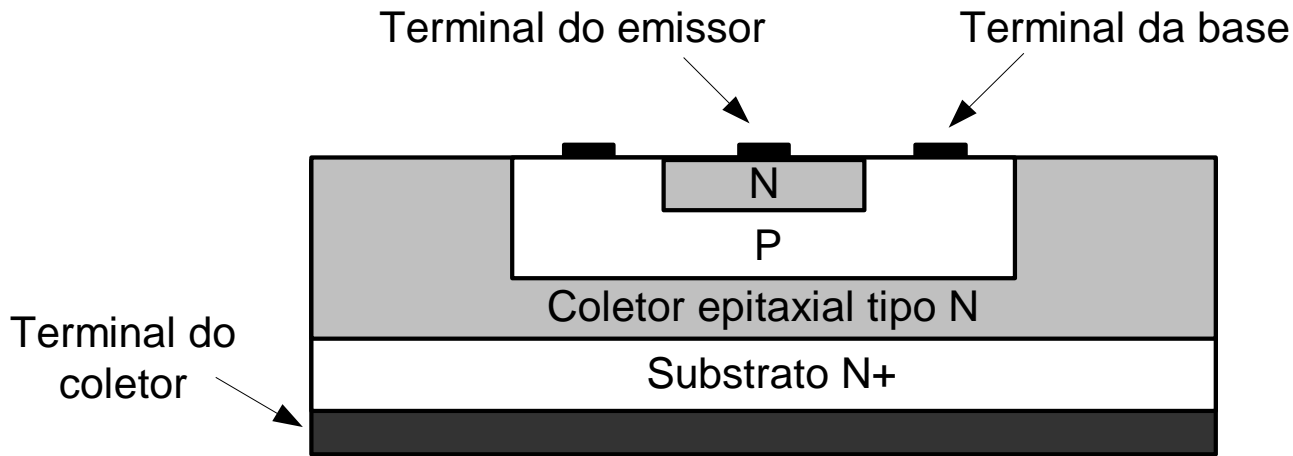
Transistores bipolar NPN e PNP



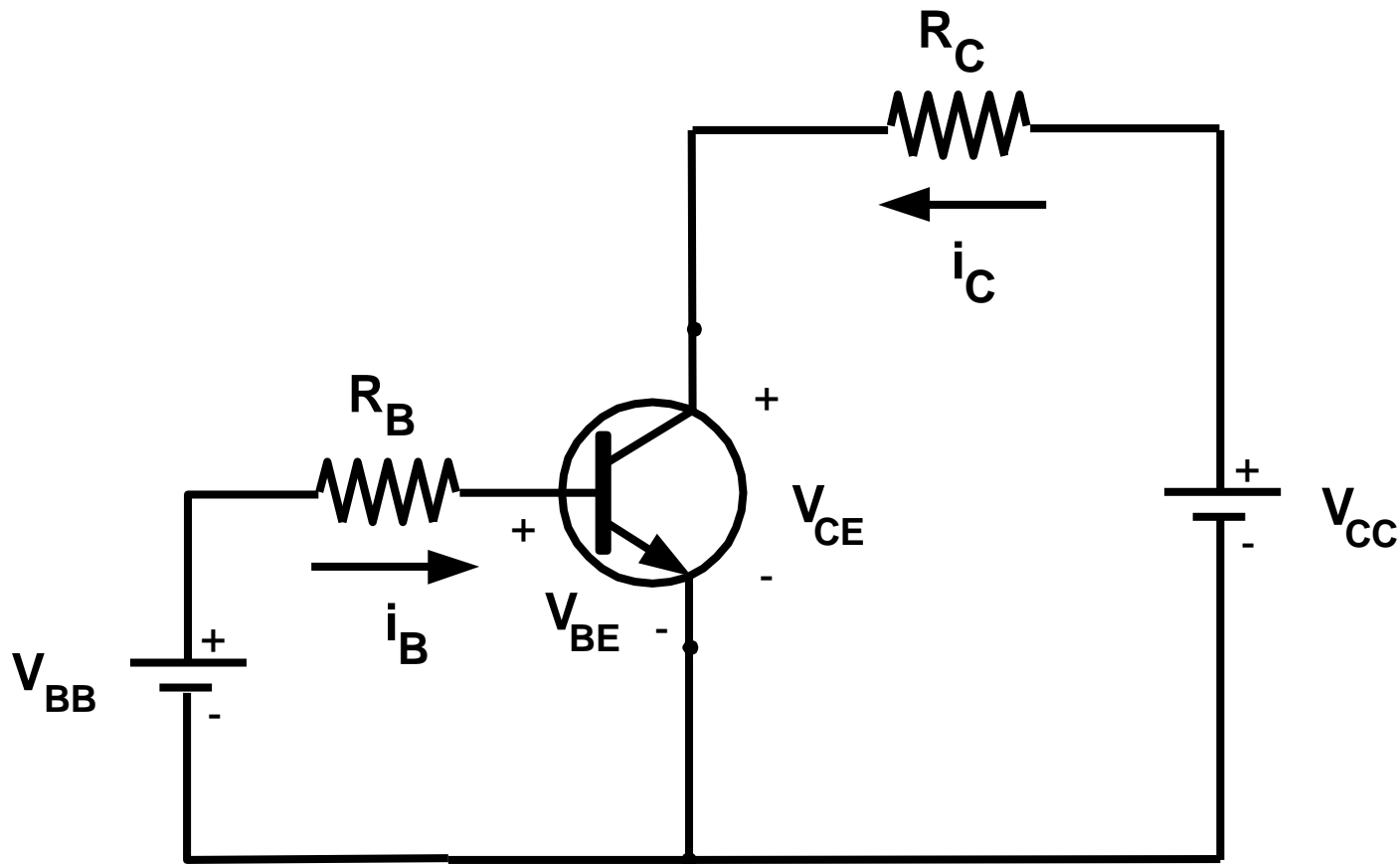
Transistores bipolar NPN e PNP



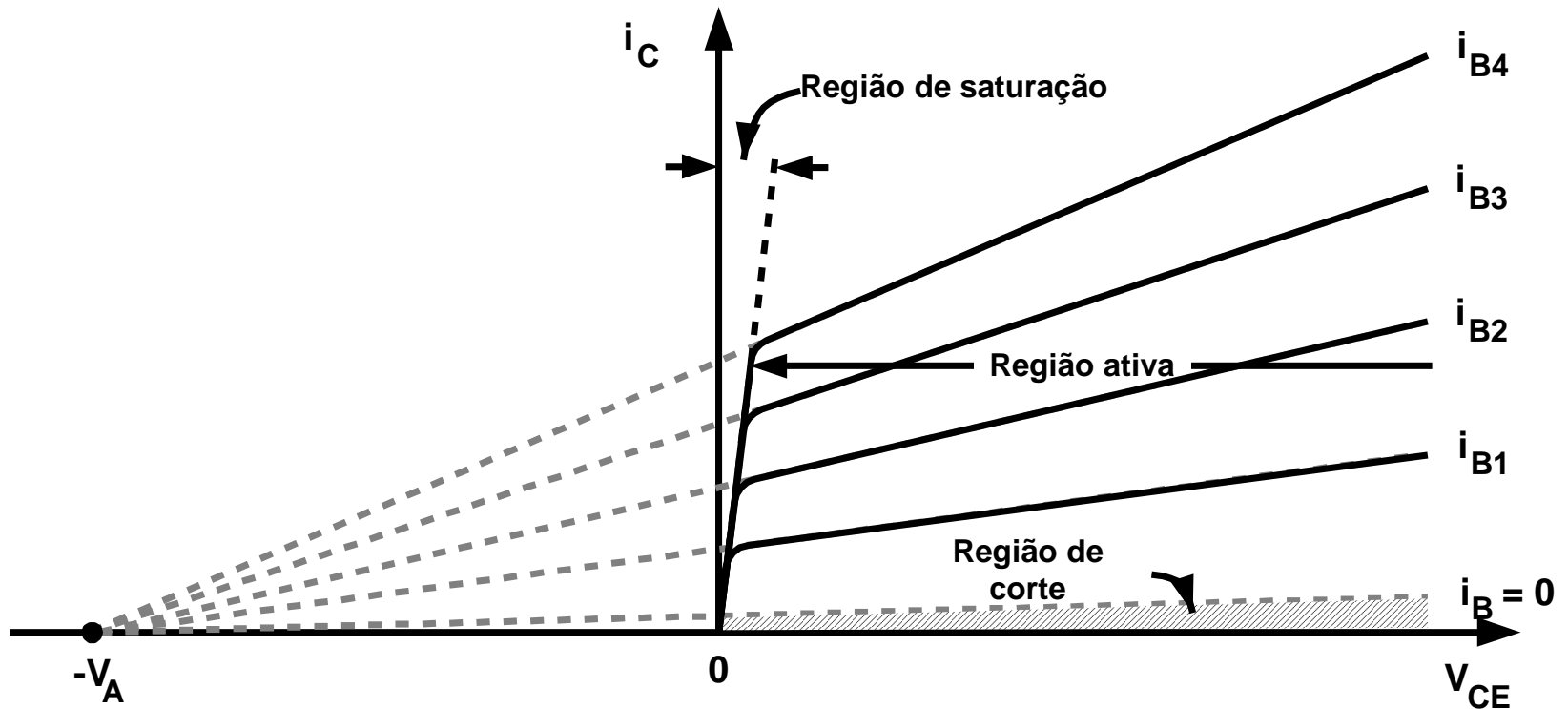
Transistor NPN epitaxial planar



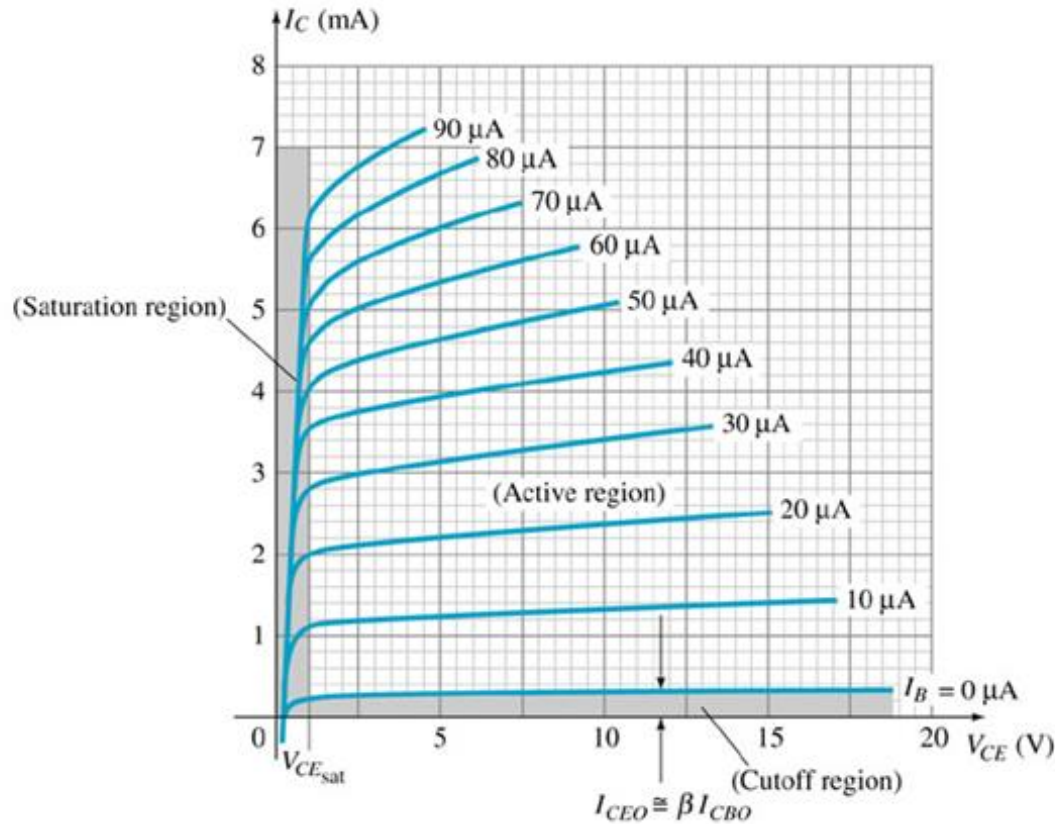
Circuito de polarização do transistor bipolar



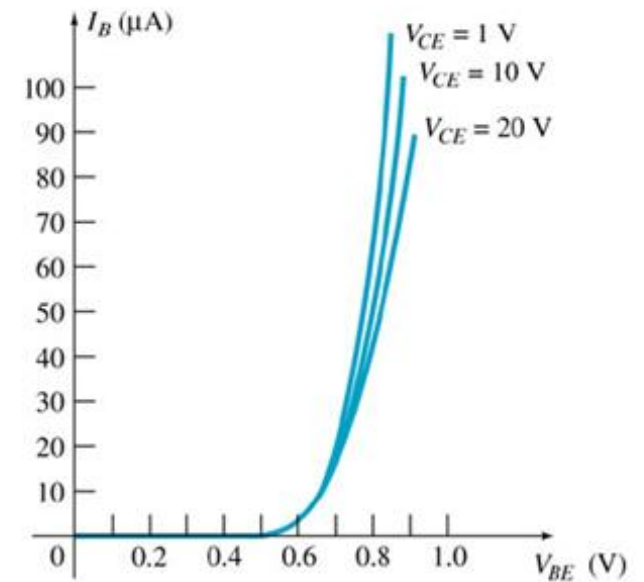
Curva I_C - V_{CE} do transistor bipolar



Curvas características I-V do transistor bipolar NPN: configuração emissor comum



(a)



(b)

Datasheet do transistor 2N4123

2N4123, 2N4124

General Purpose Transistors

NPN Silicon

Features

- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage 2N4123 2N4124	V_{CE0}	30 25	Vdc
Collector-Base Voltage 2N4123 2N4124	V_{CBO}	40 30	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current - Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

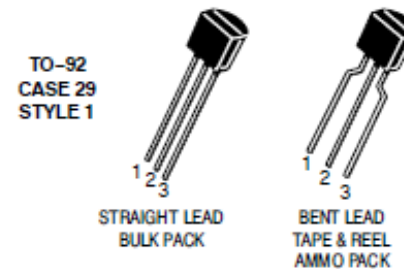
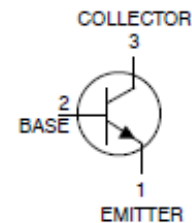
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	63.3	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

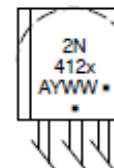


ON Semiconductor®

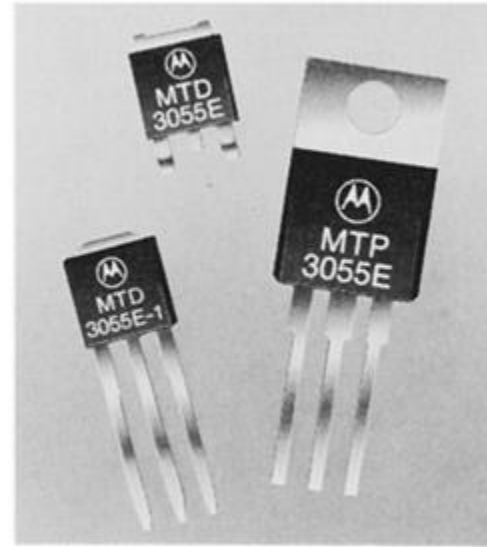
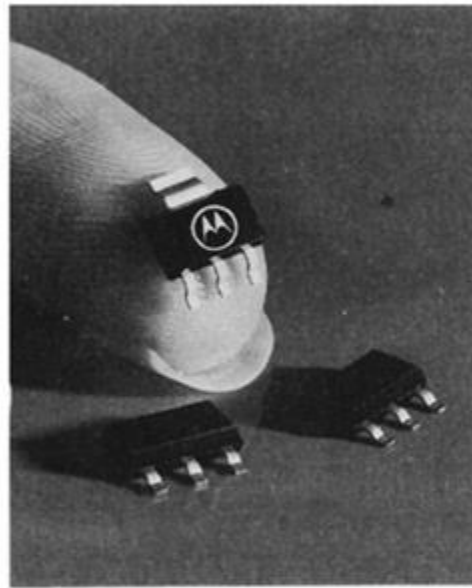
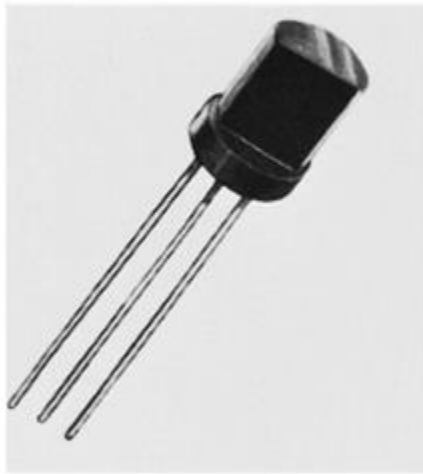
<http://onsemi.com>



MARKING DIAGRAM



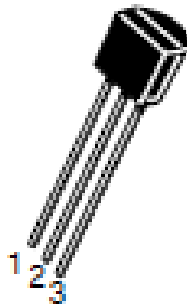
Tipos de encapsulamento de transistores



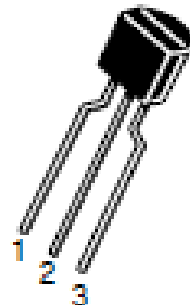
(c)

(d)

TO-18
CASE 29
STYLE 1

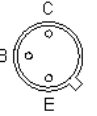
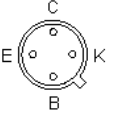
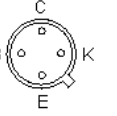
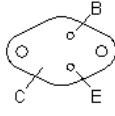
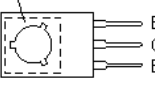
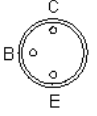


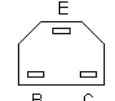
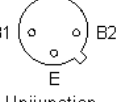
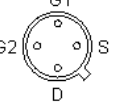

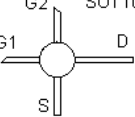
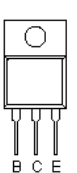
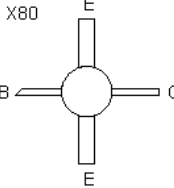
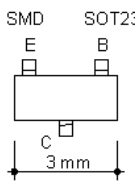


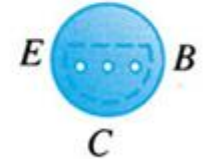
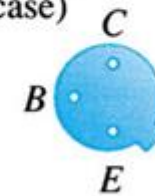
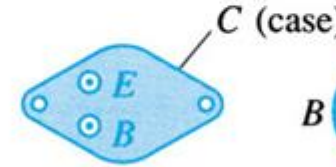
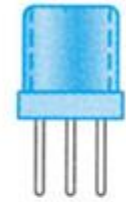
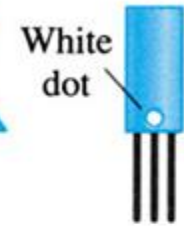
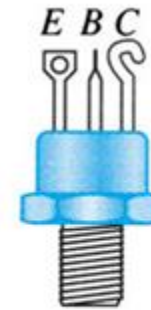
STRAIGHT LEAD
BULK PACK



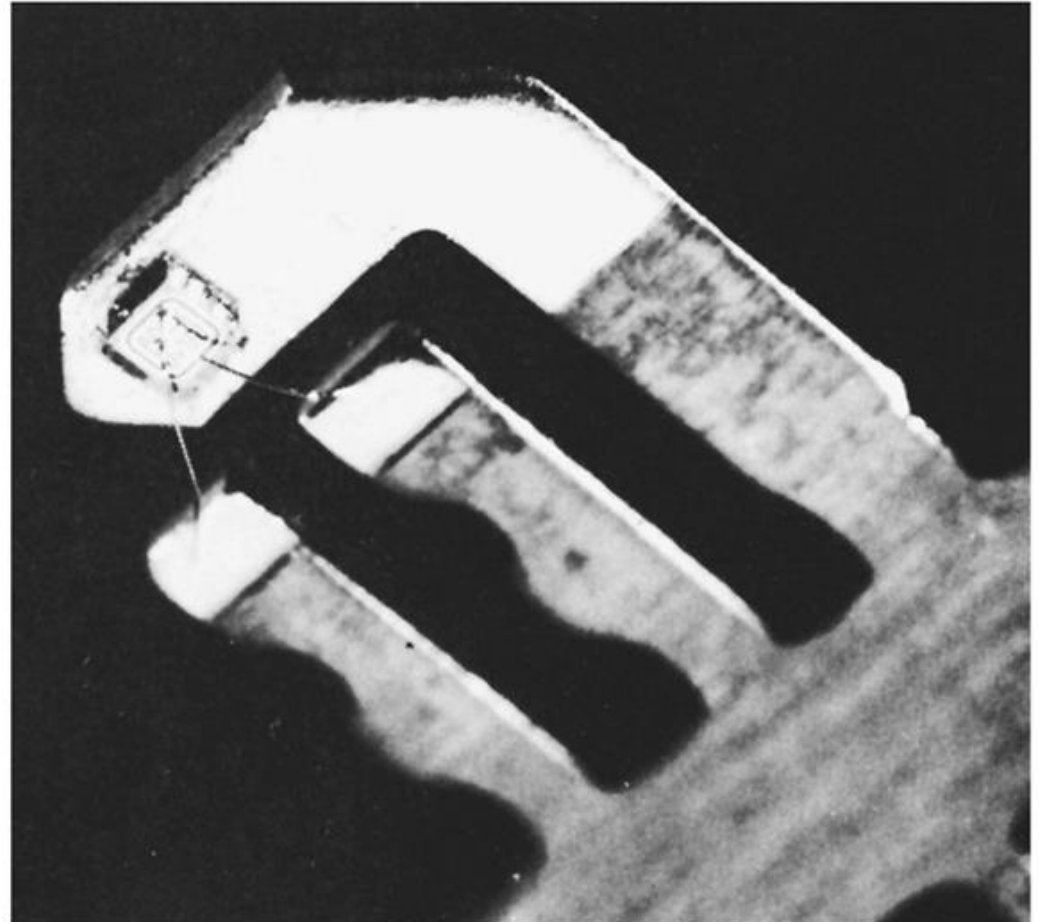
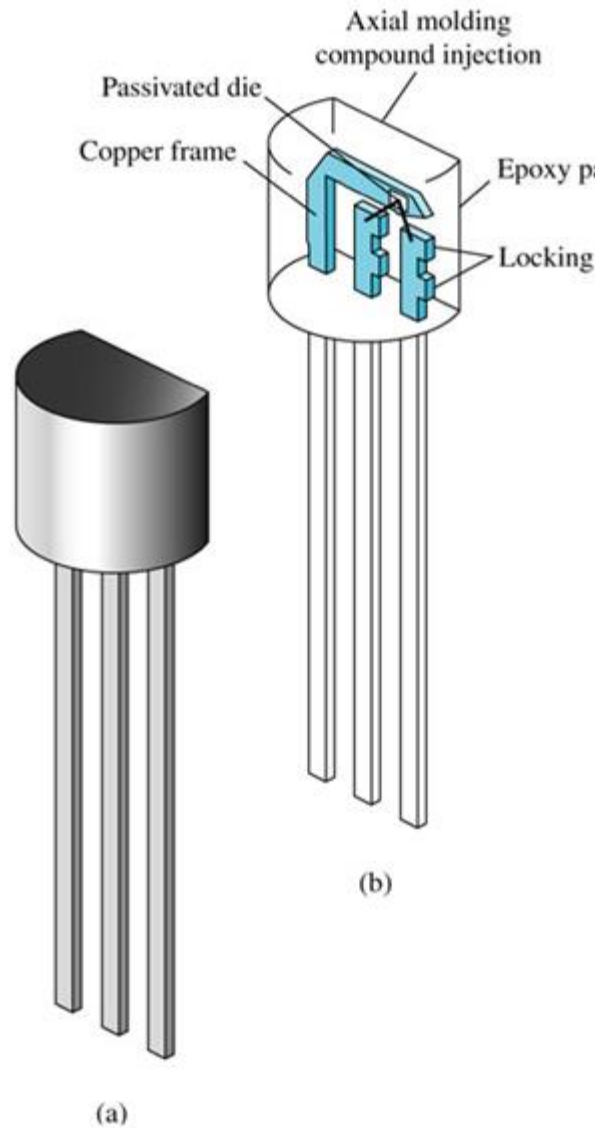
BENT LEAD
TAPE & REEL
AMMO PACK

Identificação de terminais de transistores

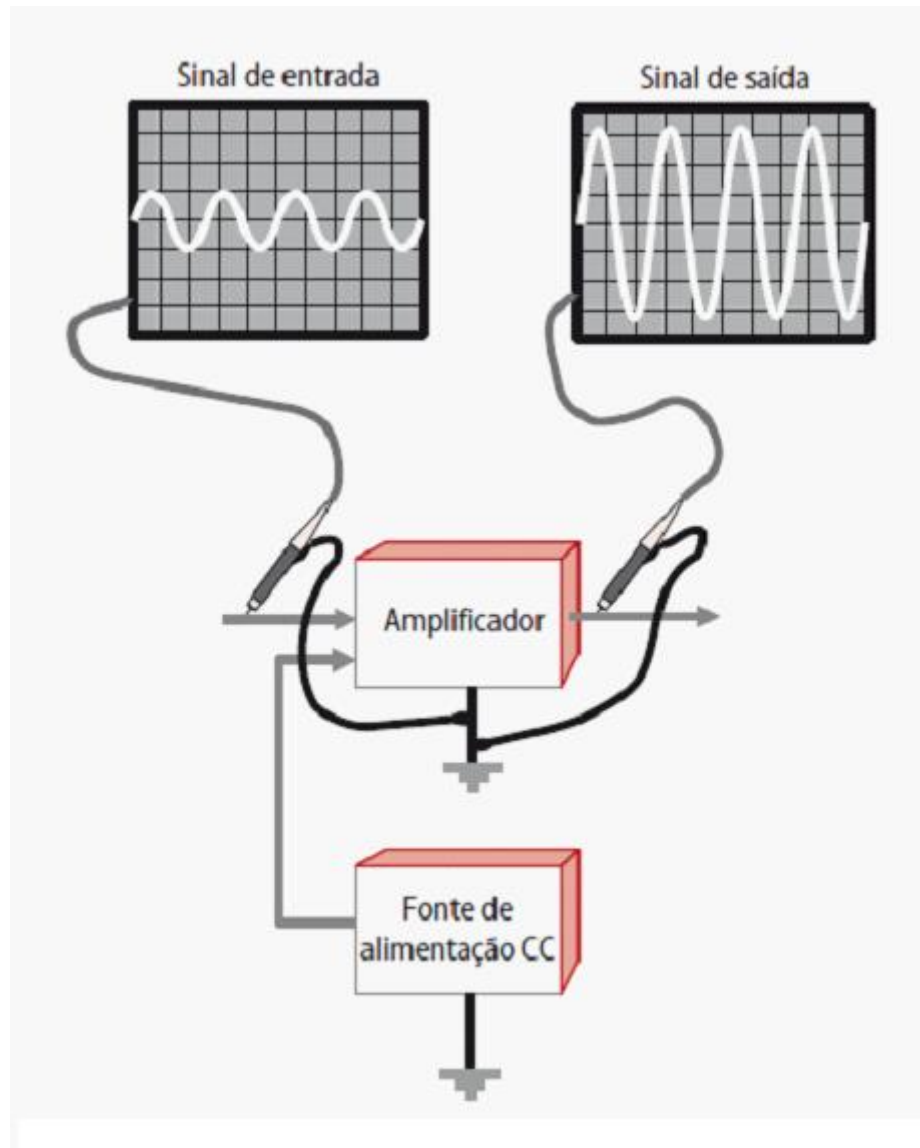
<p>Package TO5, TO18</p>  <p>NPN BC107 BC108 BC109 BFX84 BFY50 2N706 2N2869 BC286</p> <p>PNP BC177 BC179 BC186 BC187 BCX88 BCY71 BC287 2N2904</p>	<p>TO72</p> <div style="display: flex; justify-content: space-around;"> <div data-bbox="318 321 569 564">  <p>NPN PNP BF180 BF182 BF183 BF200</p> <p>AF139 AF178 AF179 AF180 AF181</p> </div> <div data-bbox="589 321 811 564">  <p>NPN PNP BF115 BF167 BF173 BF184 BF185</p> <p>AF124 AF126 AF127</p> </div> </div>		<p>TO3 and similar</p>  <p>NPN PNP 2N3055 BDY20 BDY21 BDY23 AD161</p> <p>PNP3055 BDX18 OC26 AD149 AD162</p>	
<p>TO126</p>  <p>NPN BD136 BD137 BD437 BUP41</p> <p>PNP BD136 BD137 BD438</p>	<p>TO-1</p>  <p>NPN PNP AC176 AC187</p> <p>AC128 AC188</p>	<p>X-55</p>  <p>NPN PNP BC182 BC183 BC184 2N3707 2N3710</p> <p>BC212 BC213 BC214 2N3702 2N3703</p>	<p>TO92</p>  <p>NPN PNP BC183L BC213L BC237B BC247B BC248 BC546 2N3705 2N3903</p>	<p>SOT25</p>  <p>NPN BF184 BDY195 BDY197</p>
<p>TO18</p>  <p>Unijunction transistor 2N2646 2N2647</p> <p>2N4870 2N4871</p>	<p>G1</p>  <p>3N140 3N141 40673</p>	<p>D S G</p>  <p>BF256 2N3819 (connection FET)</p>	<p>G2 SOT103</p>  <p>BF960 BF961</p> <p>BF981 3SK81</p>	<p>NPN PNP</p> <p>BC157 BC158 BC159 BCX35</p> <p>BC147 BC148 BC149 BCX31</p>
<p>TO220</p>  <p>NPN BD539 BD743 TIP29C BU407 BUP30 2N6099 BD243C D44C10 BD241C</p> <p>PNP BD540 BD744 TIP30C BD244C BD240C BD242C</p>		<p>X80</p>  <p>BFR14 BFR49</p>	<p>SMD SOT23</p>  <p>NPN PNP BC846B BC847B BC848B BC849B</p> <p>BC856B BC857B BC858B BC859B</p>	



Construção interna de transistores



Esquema de um amplificador de sinal



Transistor bipolar como amplificador

